



Power Electron Tubes as an Enabling Technology for the Grid

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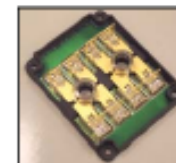
Overview

- Advanced Fusion Systems LLC (AFS) is developing a series of products for the power electronics market to replace semiconductor devices.
- Semiconductor devices have a number of well-known deficiencies which limit their utility in power electronics applications.
- AFS is currently constructing a 250,000 square foot facility to manufacture power electronics electron tubes and systems in large quantities.
- Initial power industry product offerings will include:
 - Pulsatron™ - replacement for Thyristor Press-Packs & GTO devices
 - Bi-tron™ - replacement for IGBT
 - *Faultron*™ Combination Fault Current & Over-voltage Limiter
 - Bulkhead Mount Transient Suppressors (E1 rated)
 - HVDC to 3 ϕ HVAC Inverters (Voltage Source Converters)
 - EMP & GIC Protective Devices
- The AFS facility has an onsite testing capability for High Voltage (AC & DC), Fault Current, EMP, GIC, Flashover and numerous other tests common to the utility industry requirements.



- End of Semi-conductors reign due to superiority of electron tubes in every way
- Can be used in direct replacement for Thyristors, IGBT's – New Circuit Topologies not previously possible
- Multitude of New Applications can be imagined
- Advanced Fusion has tremendous capability to supply market demand
- Testing and Demonstration capability as well. 25 Year Warranty, High Robustness & Reliability, 100% Inspection, Zero defects...

Advanced Power Electronics



Addresses fundamental research required for advances in PE materials

Silicon

- Widely available
- Low cost



Super GTO Switch
2007 R&D 100 Award

Silicon Carbide

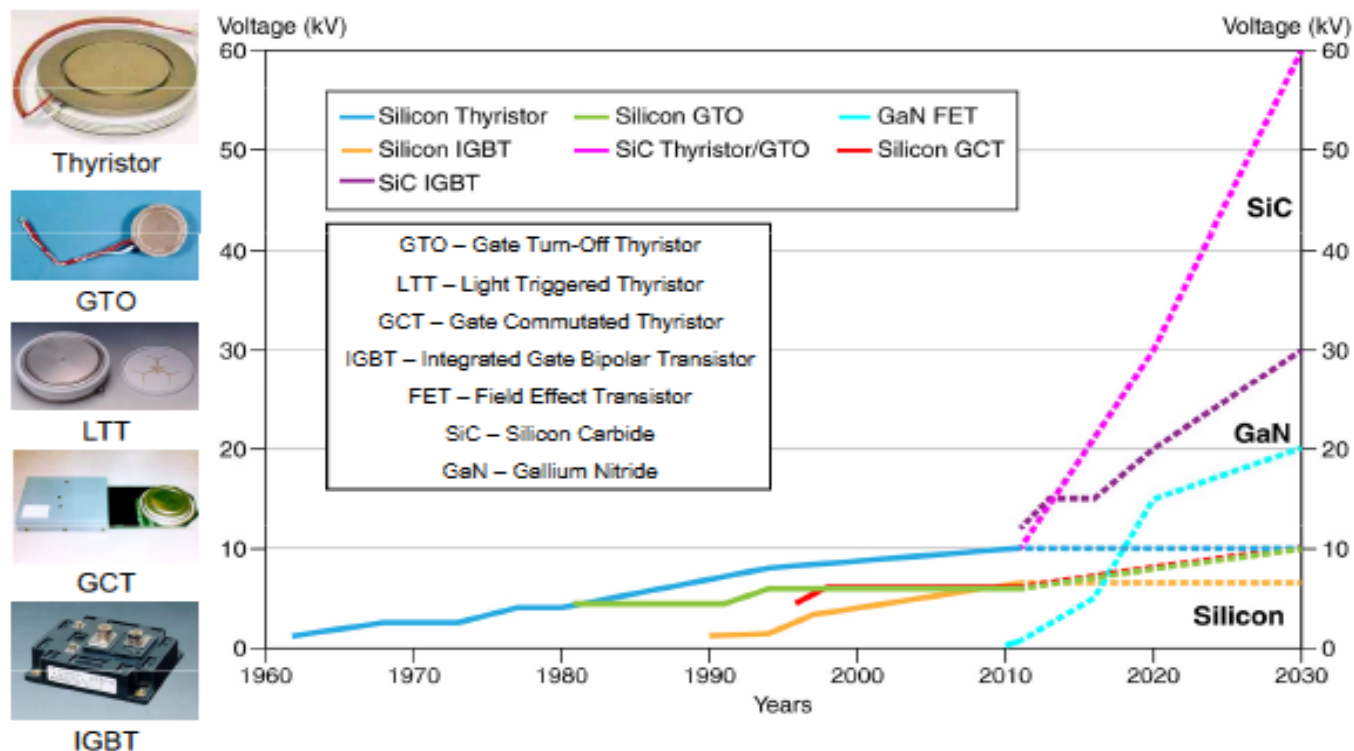
- High operating temperature
- Lower switching losses

Silicon Carbide + Gallium Nitride

- Higher Temperature
- Higher Voltage
- Optical switching

New power electronics materials enable newer applications and benefits

Technical Innovations – Power Electronics





COMPARISON OF SEMICONDUCTORS AND ELECTRON TUBES IN POWER ELECTRONICS APPLICATIONS



Electron Tubes vs. Semiconductors

- AFS electron tubes use technology originally developed for military EMP simulation & high-power microwave applications. They are designed for repeated operation in this extreme transient environment.
- The robustness of electron tubes in the EMP & transient environment is well documented.
- Solid-state devices are subject to failures arising from:
 - Piezo-electric induced over-stress .
 - Single arc failure
 - Thermally-induced overload.
- AFS electron tubes are significantly faster than the fastest power semiconductor devices allowing circuit topologies previously not considered.
- These tubes are not subject to dV/dt or dI/dt constraints as semiconductors. Typical AFS device slew rates are well in excess of megavolts per microsecond.



Semiconductors vs Electron Tubes

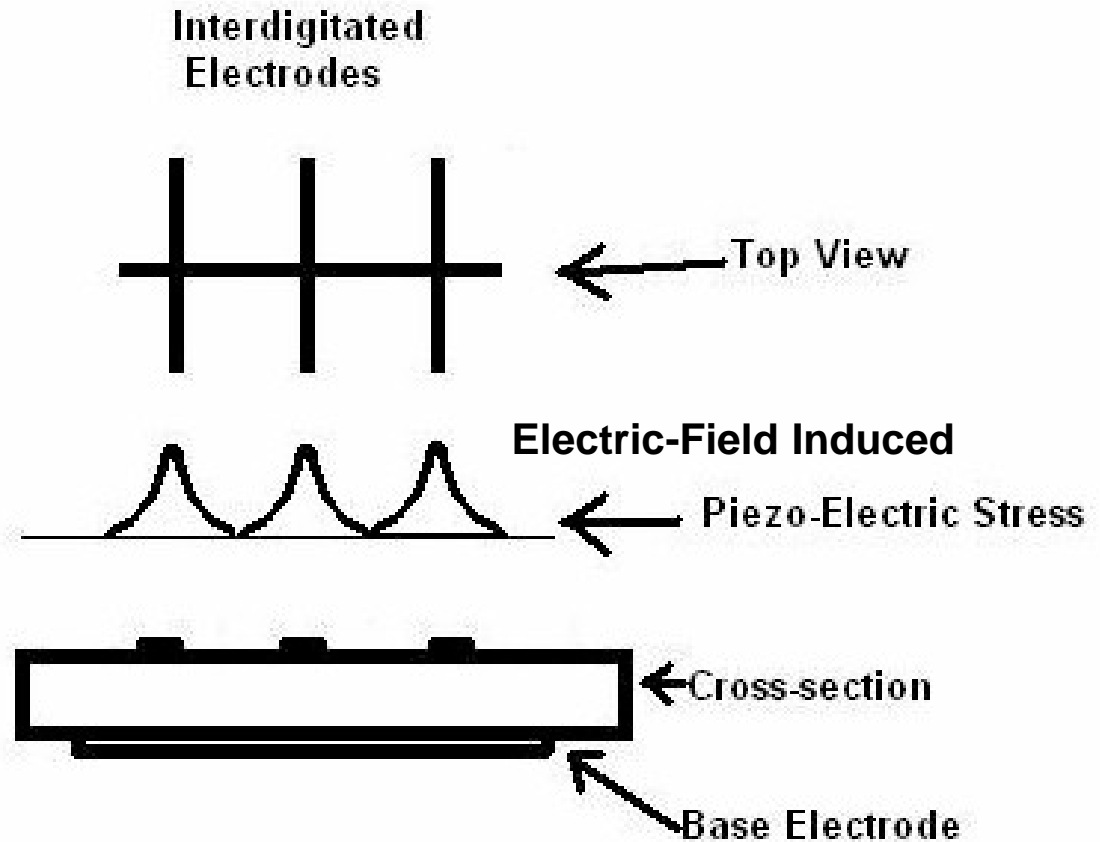
Failure Mode

Semiconductor Devices

Electron Tubes

Arcing	Fail after first arc event	Highly arc resistant
Thermal Sensitivity	Requires elaborate cooling	Can operate up to 1000° F without cooling
Voltage Handling	Individual devices limited to 20 KV	Individual devices can handle up to 1.2 MV
Current Handling	Individual devices can handle 8 KA	Individual Devices can handle >1 MA
Circuit Complexity	Very complex circuits required	Very simple circuits
Customization	?	Readily Able to Customize Ratings, Features, etc.
Warranty	?	25 Year Unconditional Warranty

Piezo-electric failure mode of semiconductor devices





Semiconductors vs Electron Tubes (2)

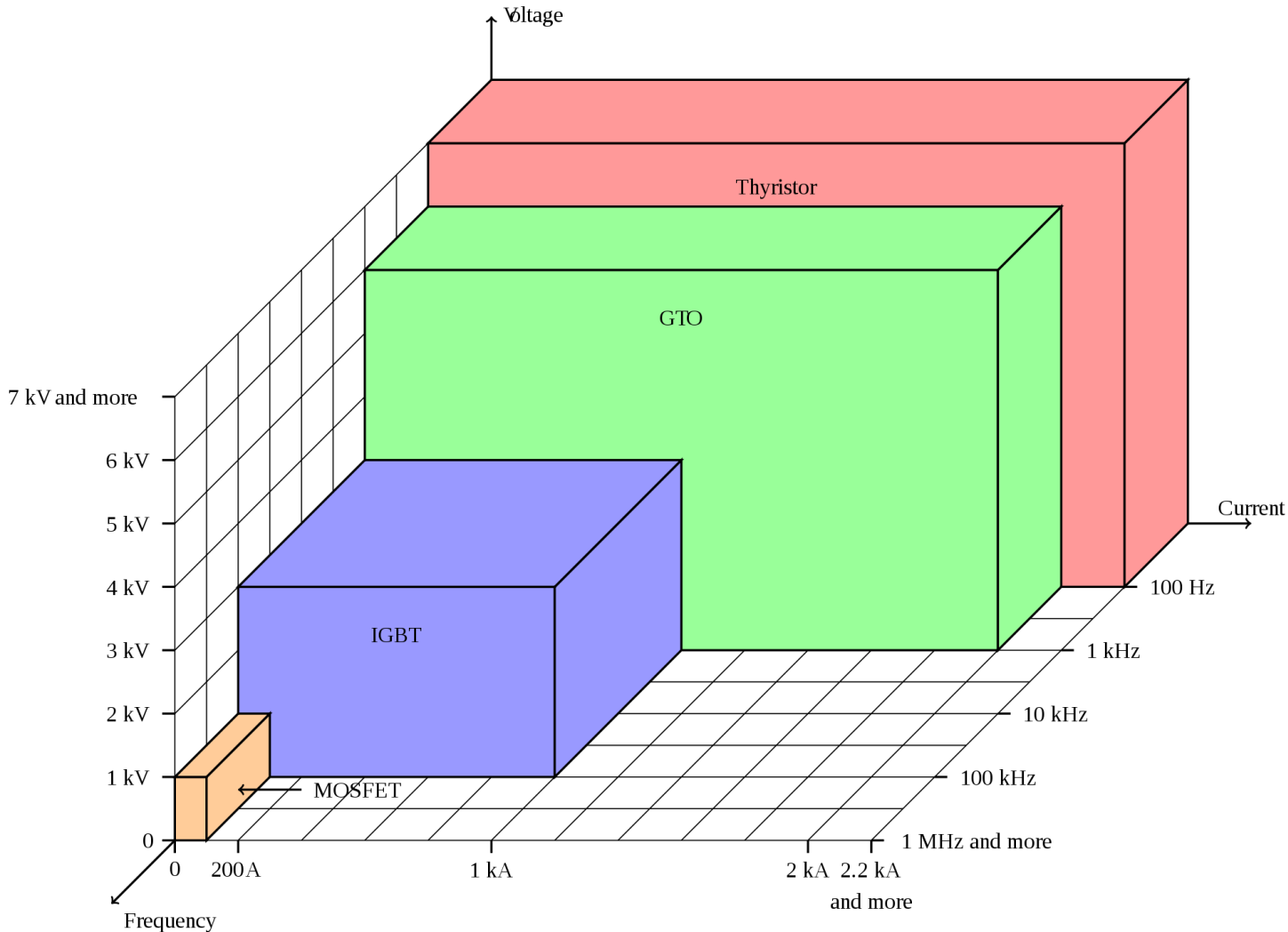
<u>Parameter</u>	<u>Power Semiconductor Devices</u>	<u>Electron Tubes</u>
Voltage	<20 KV	> 1.2 MV.
Current	<20 KA	>> 1 MA
Max Frequency	KHz	GHz
Max Temp.	25 ^a C (Si); 200 ^a C (SiC)	500 ^a C
Arc Resistance	None	Highly
Energy Capacity	10's of KiloJoules	10's of MegaJoules
Losses	Typically 0.5 > 0.7 V/junction	~5 eV per device (1 eV = 1.6×10^{-19} J)

The Electron Tube compared to Semi-Conductor Devices

Current/Voltage/switching frequency domains of the main

“Semi-Conductor” based power electronics switches

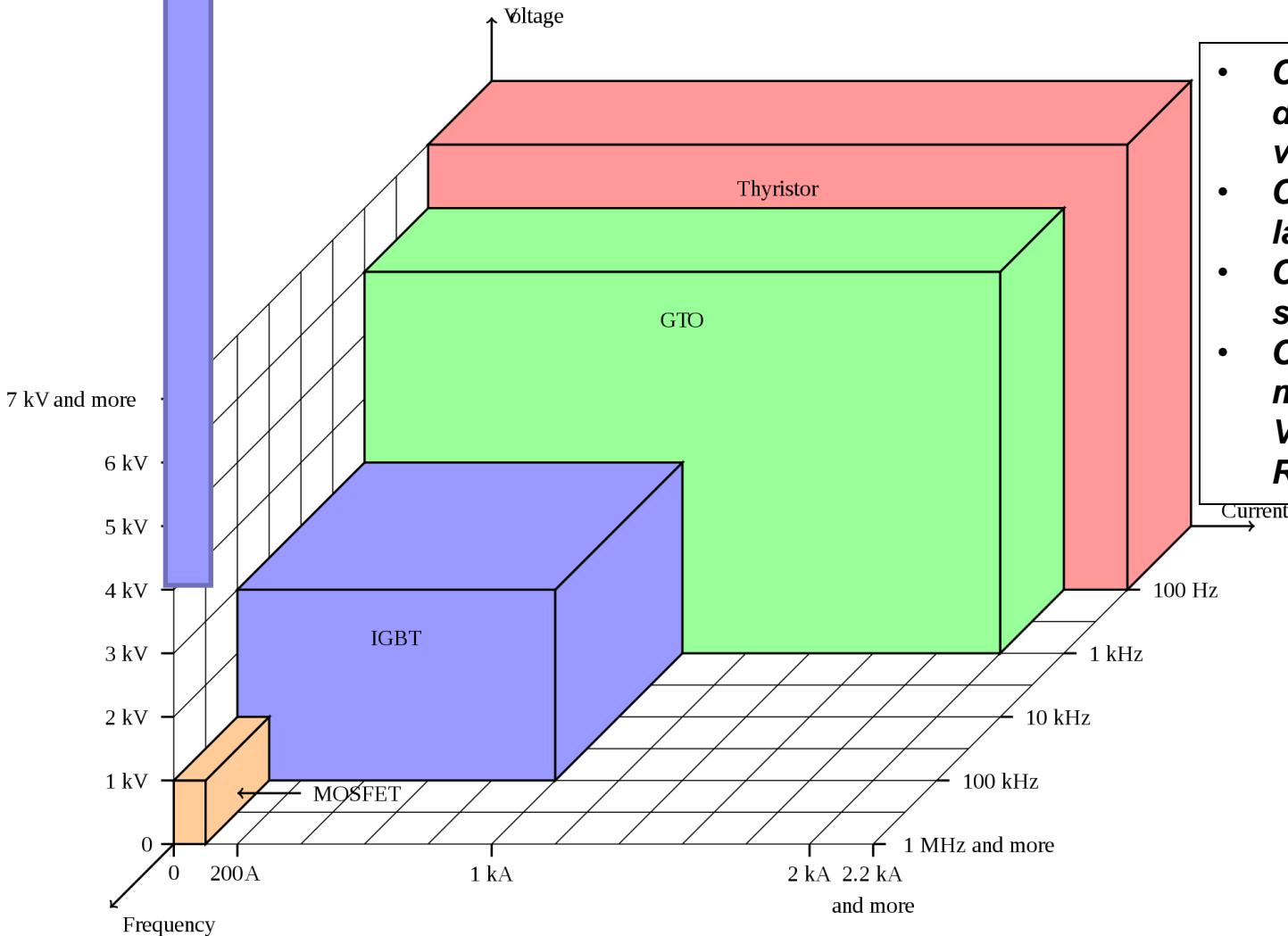
(note some ratings for select devices could be higher than represented in these graphs)



The Electron Tube compared to Semi-Conductor Devices

Voltage Ratings can Span from 4kV to 1000kV per device

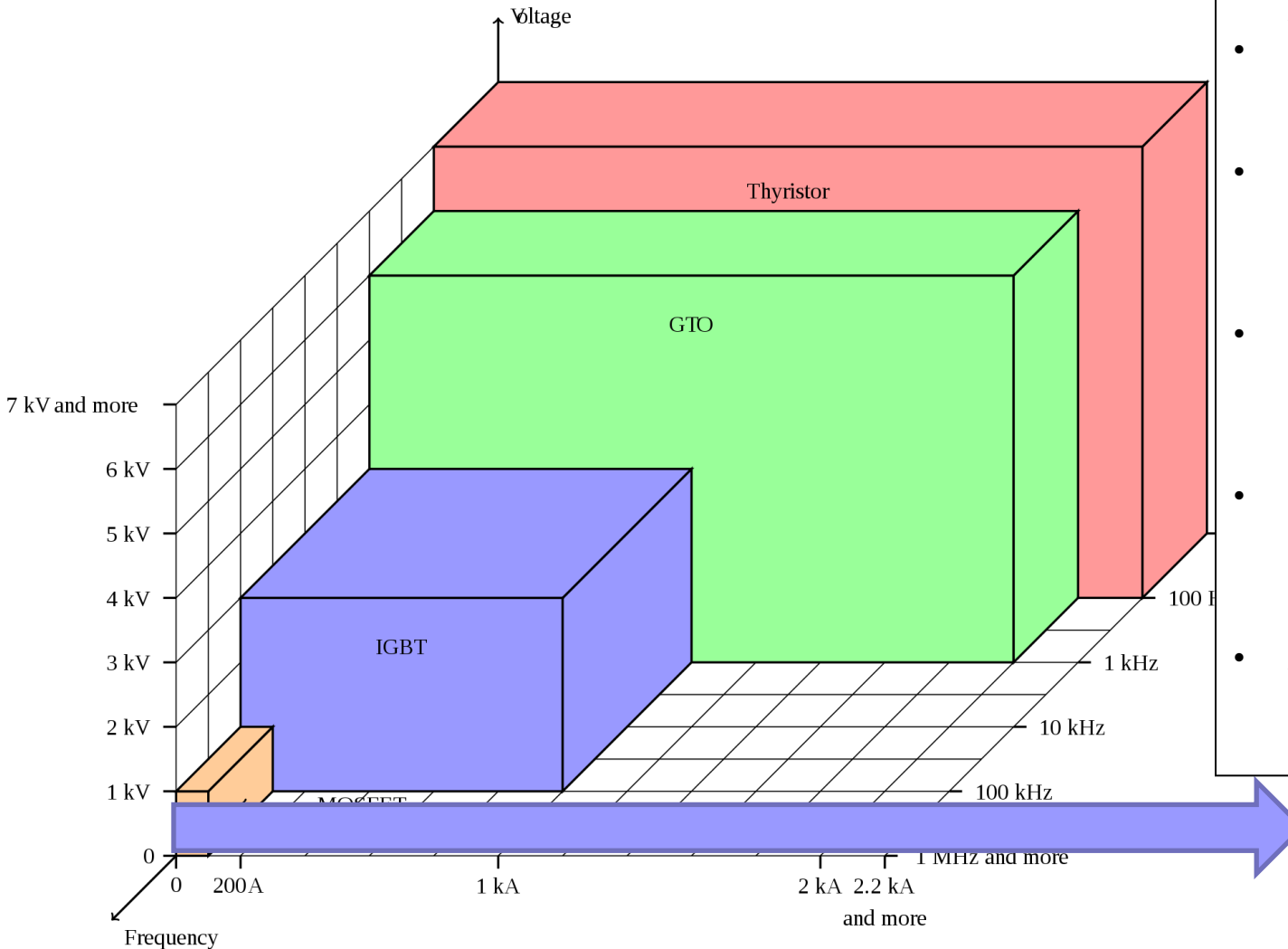
ADVANCED FUSION SYSTEMS



- **Cathode dimensions determine allowable voltage ratings**
- **Cathodes can be very large (>2000cm²)**
- **Cathodes can be quite small (<1mm²)**
- **Can be custom sized to meet requirements for Voltage and Current Ratings**

The Electron Tube compared to Semi-Conductor Devices

Current Ratings can Span beyond 100kA

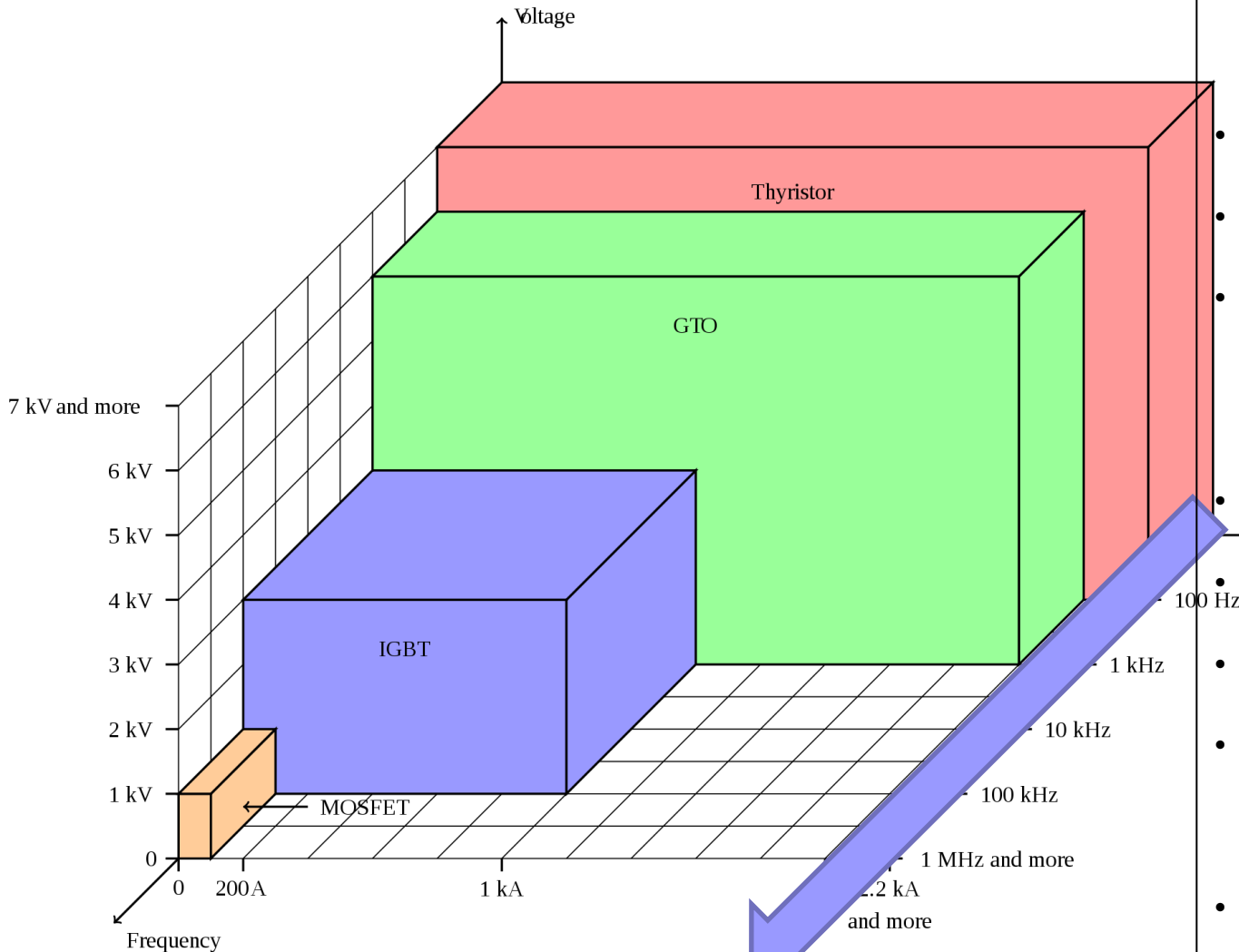


- **Continuous current ratings of 500 Amps/cm²**
- **Pulse Mode or short duration ratings of 81 kA/cm²**
- **Design flexibility allows for Tube Devices with Continuous Current Ratings of >>10kA**
- **Tubes have very low losses (150 micro-ohms steady state), also low switching loss**
- **Cathodes as large as 1800cm² have exhibited long life under extreme duties**
- **Advanced Fusion backs device with 25 Year Unconditional Warranty**

The Electron Tube compared to Semi-Conductor Devices



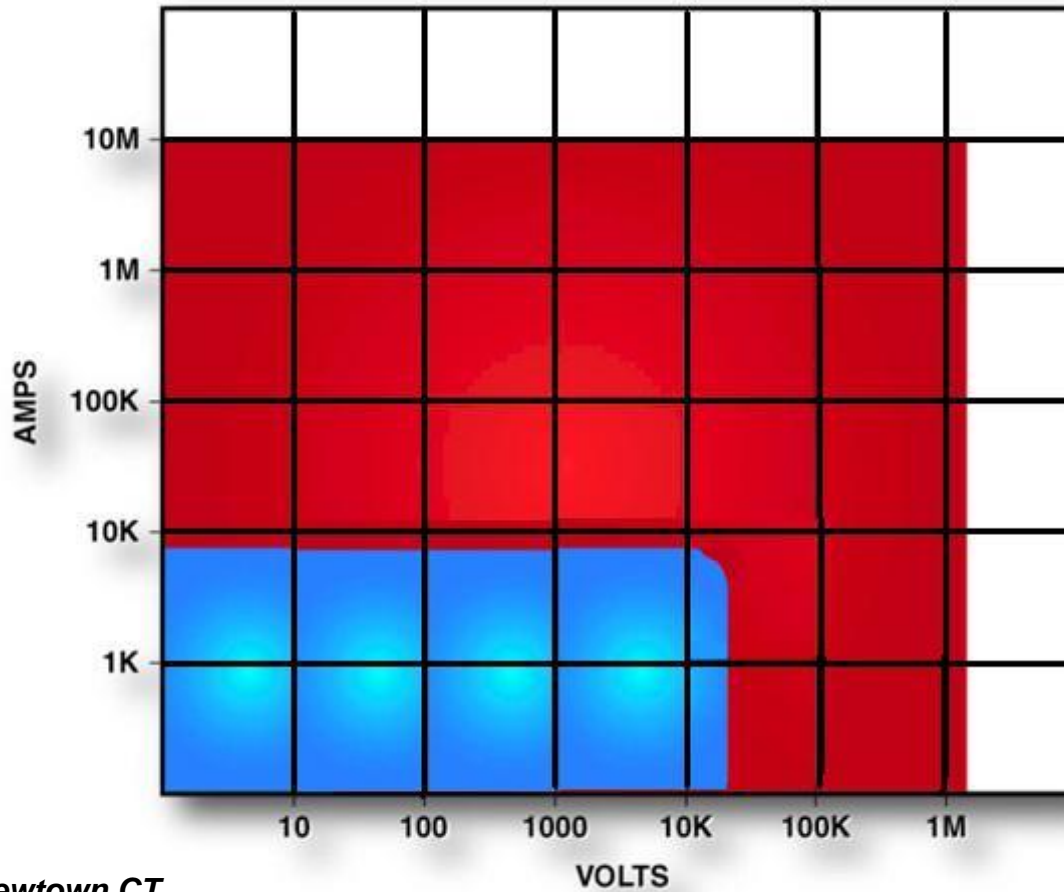
Frequency Ratings can Span from DC to 3GHz



- **Can be switched on, switched off and all CW & Pulse operating modes**
- **Can switch with 100 picosec risetime**
- **10 microsec pulse width**
- **Tube Device does not have di/dt or dv/dt design limitations common in semiconductor devices**
- **Does not need snubber auxiliaries**
- **Can operate to temperatures of 1000°**
- **No need for cooling systems**
- **Can also tolerate arc over without failure (unlike semiconductor devices)**
- **Withstand 300G shock forces**



*Electron Tubes (Red) vs.
Semiconductors (Blue):
Single Device Voltage vs.
Current Continuous Capacity*



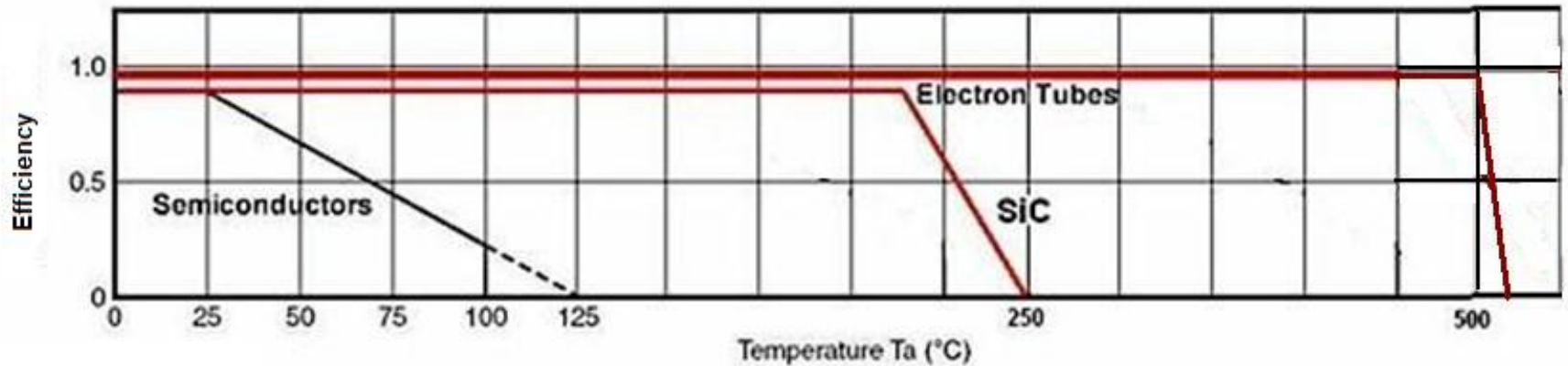


Semiconductors vs Electron Tubes (3)

- AFS electron tubes can replace semiconductors in virtually every circuit configuration.
- These tubes have turn-on, turn-off, and modulation modes.
- AFS electron tubes require very little cooling due to their high operating temperature rating due to higher efficiency and refractory construction.
 - Cooling not required below 1000[⊕] F operating temperature.
 - No fall off in performance below maximum operating temperature
- These tubes have orders of higher energy handling capacity due to their refractory construction.
- Voltage and Current Limiter configurations available in all voltages and currents, AC & DC.



Thermal efficiency of power devices



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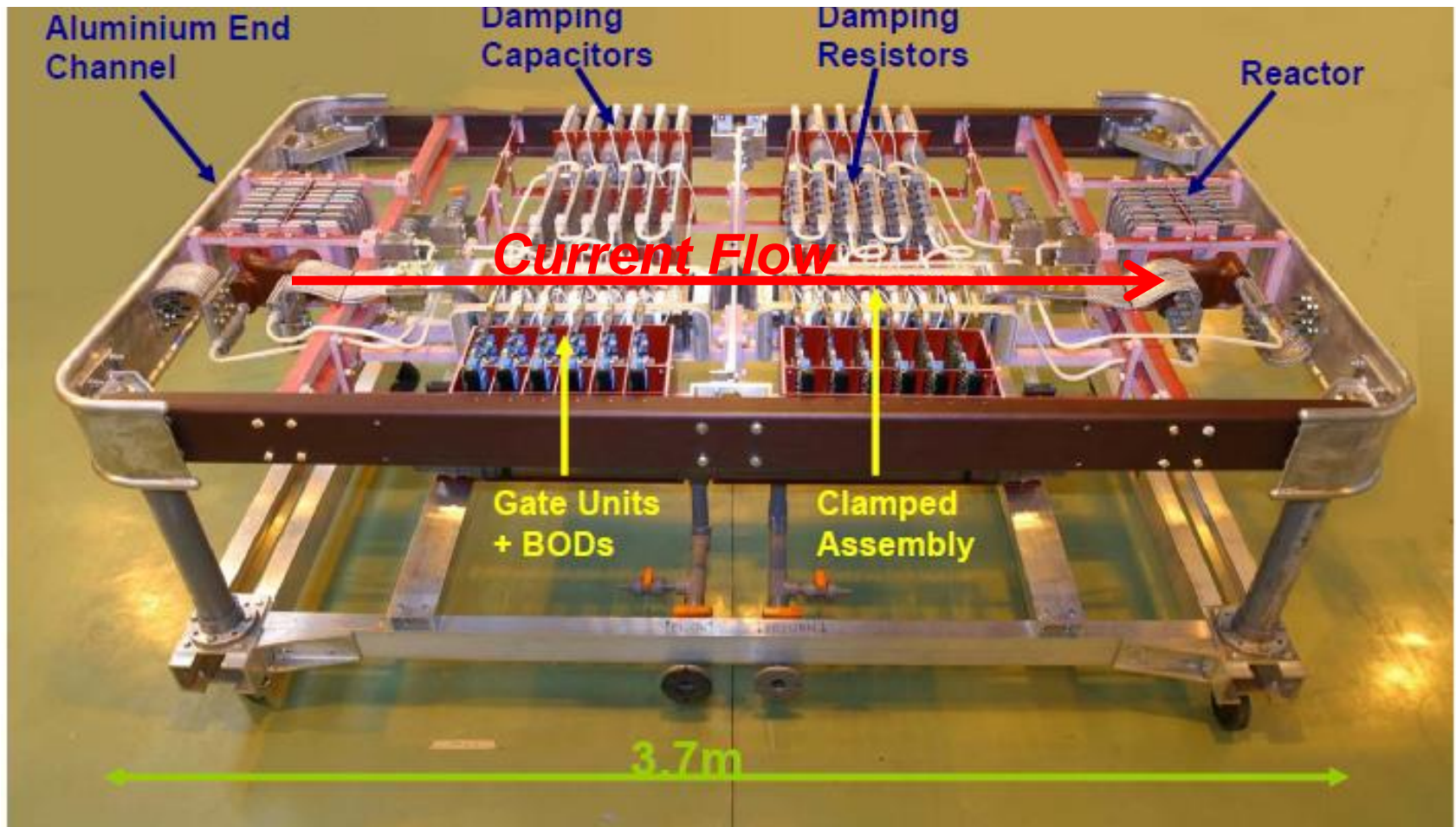
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Example 660kV Thyristor Valve



Example Thyristor Valve Section

- *Enormous amount of auxiliaries for control, snubbers and cooling and indoor environment housing which*
- *Add costs, complexity, losses, reduces reliability and have lead to catastrophic failures*





ELECTRON TUBE DEVICES



PULSATRON™



3275 Pulsatron™

- The *Pulsatron*™ is a high vacuum, cold-cathode triode electron tube. It is designed for high-speed, high-power operation
- Specifications:
 - DC to 3 GHz
 - 500 KV Max
 - 250 KA Max
 - <100 picosecond risetime
 - 10 μ Sec pulse width
 - > 500 KHz pulse mode
 - CW Mode
- Compact: 5" 12", 5lbs



**^ Pulsatrons
(Block 3)**

**< High Speed
Class A Amp**



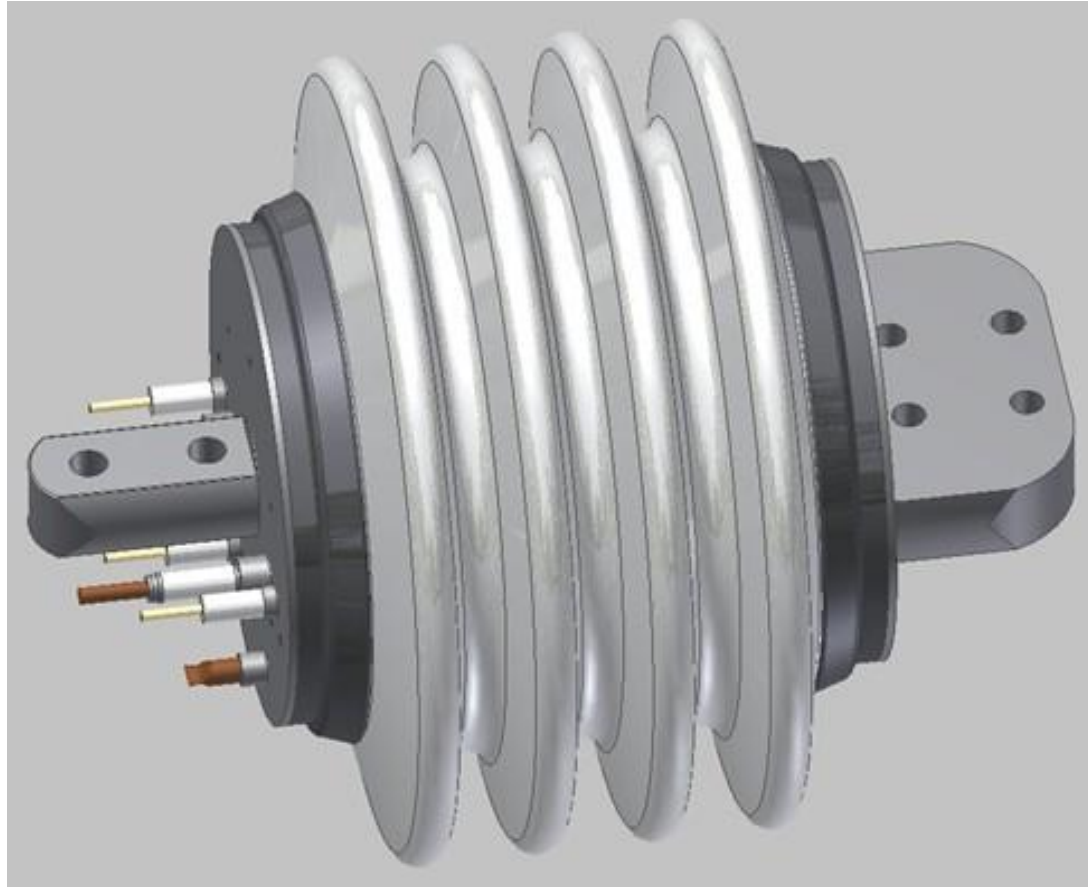
Bi-tronTM *pat pending*



4275 Bi-tron™

- The *Bi-tron*™ is a high vacuum, cold-cathode tetrode electron tube. It is designed for bipolar high-speed, high-power **shunt** operation, and is physically similar to the 3275 except for the extra grid terminal.
- Specifications:
 - 1200 KVAC Max
 - 750 KA Max
 - <100 pSec risetime
- Size varies with voltage. Units below 35 KVAC are 8 - 12 inches in diameter and 12 - 18" long. Units for 1250 KVAC operation are approximately 6 feet in diameter.
- Units under 2 feet in diameter have external control circuits. Larger units have the control circuitry mounted internally.
- All systems have dual vacuum pumping systems.
- All systems provide an external control signal to trip external protective systems.
- All systems are self-resetting and are capable of withstanding and protecting multiple events in rapid succession.
- These devices also protect against lightning of all voltages.

4275 Bi-tron™



35 KV
100 KA



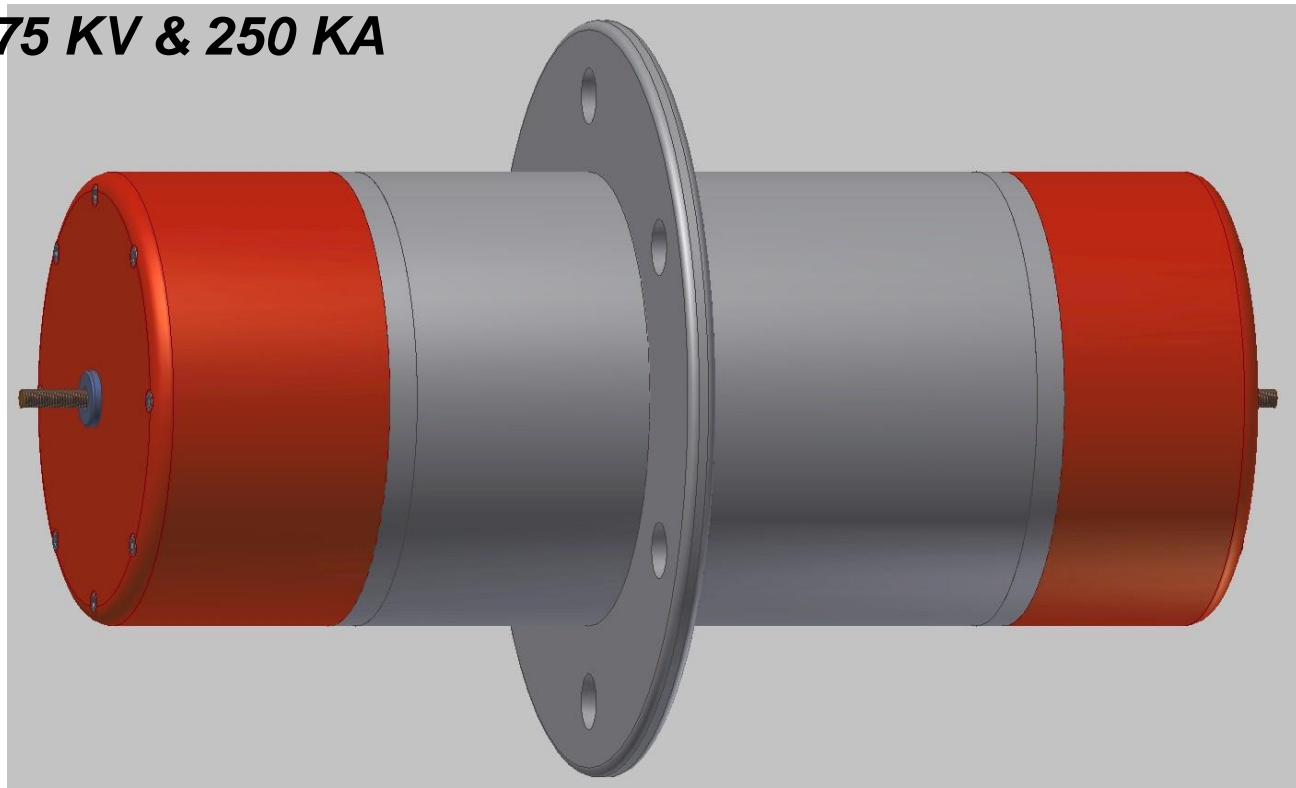
4138 Bi-tron™

- The 4138 is a patent-pending bulkhead mounted version of the Bi-tron designed for **series** insertion in transient suppressor applications.
- It retains the electrical characteristics of the 4275, but is packaged in a housing optimized for bulkhead mounting as a shielded protective feedthrough.
- The design substantially exceeds the Mil188-125 specification.
- Available to 75 KV and 250 KA.
- This tube is designed for transient suppressor & E1 EMP protection.



4138 Bulkhead Mount Transient Suppressor & EMP Protector

***Substantially exceeds MIL-188-125
Available to 75 KV & 250 KA***





APPLICATIONS

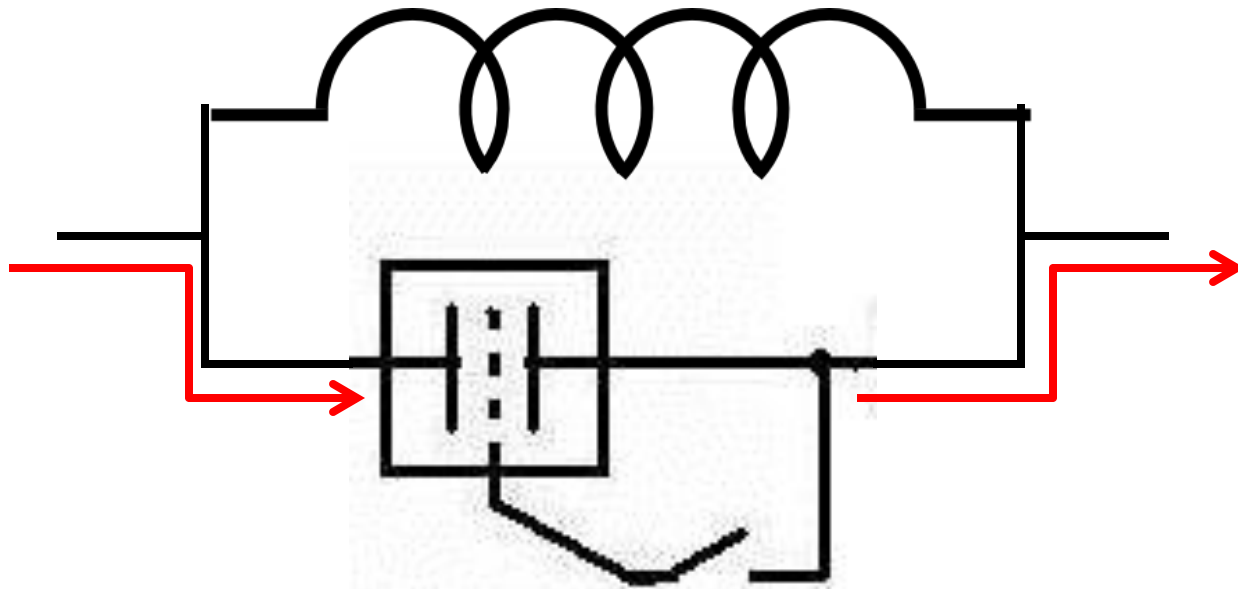


Current Regulation

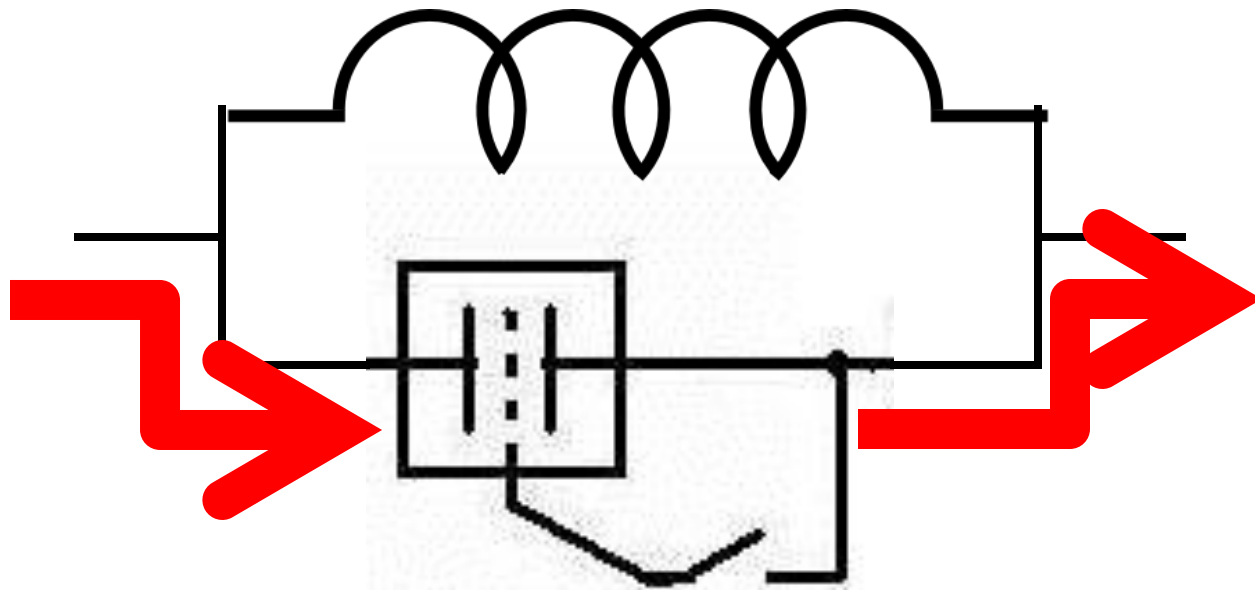
Fault Current Reduction (Distribution to EHV)

Transmission Voltage Power Flow Regulation

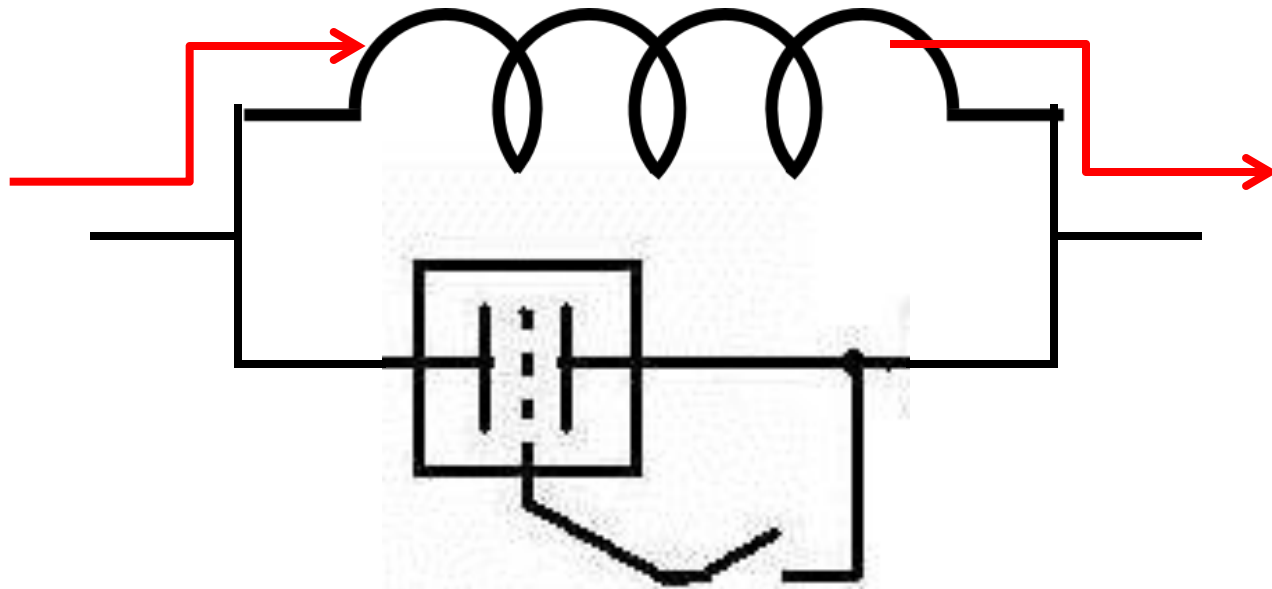
Fault Current Reduction (Distribution to EHV)



***Normal AC Current Flow
Through BiTron***

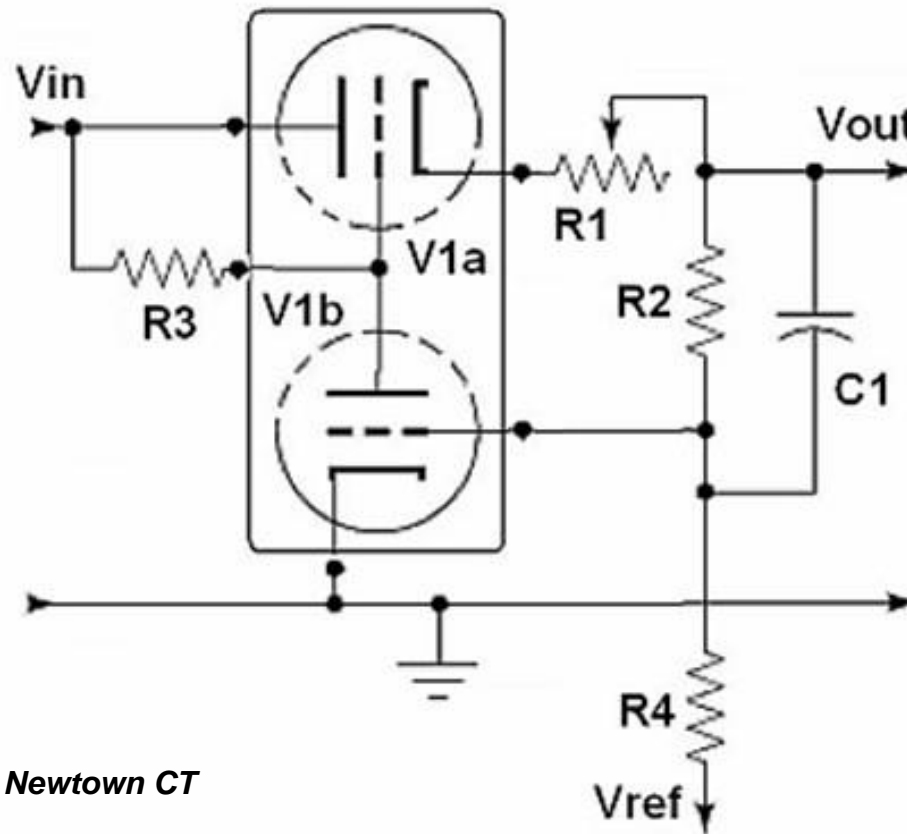


***Beginning of Hi AC Fault Current Flow
Through BiTron***



***AC Current Flow Diverted to Reactor
When BiTron Rapidly shuts off***

DC Current Regulator^{pat pend}

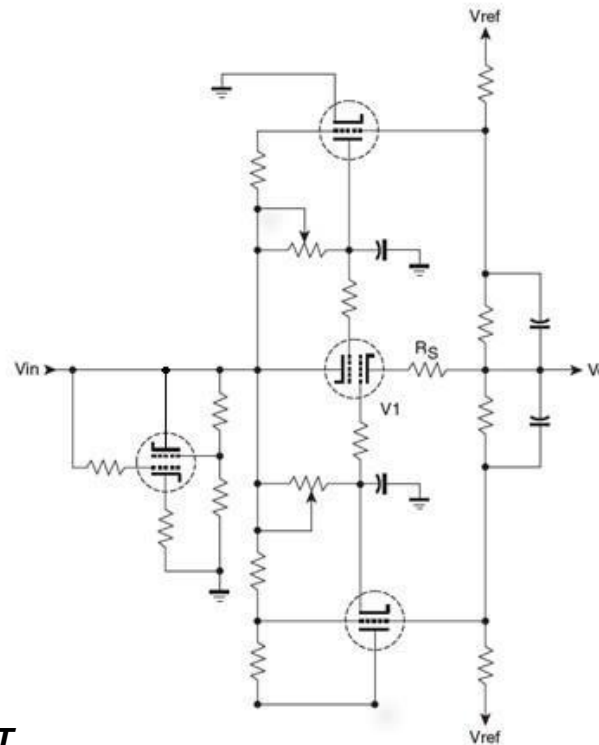




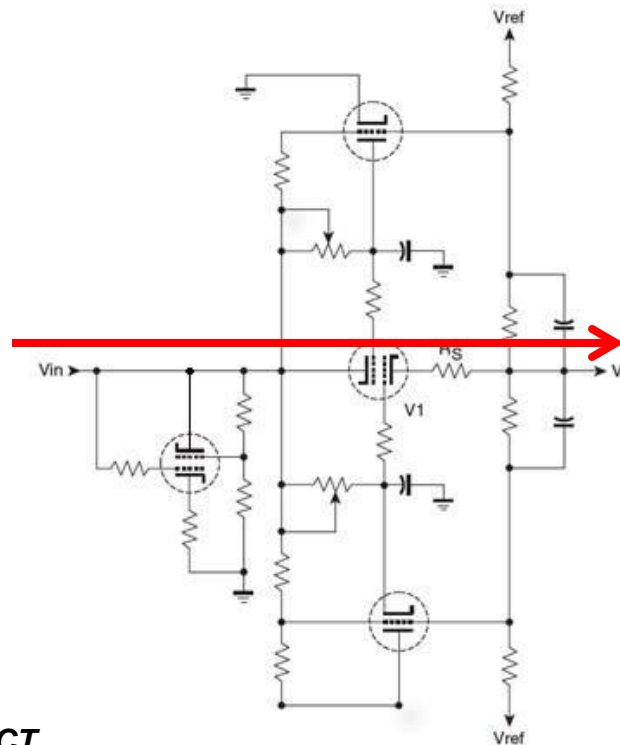
Combined Over-voltage & Over-current Limiter

- Integrated fault-current and overvoltage protection device.
- Available in all voltages from 4160 V to 1.2 MV
- Current ratings to 100's of thousands of Amps
- Robust stainless steel enclosure
- Arc-resistant technology
- Operating temperature to 1000° F before cooling

Combined Over-voltage & Over-current Limiter



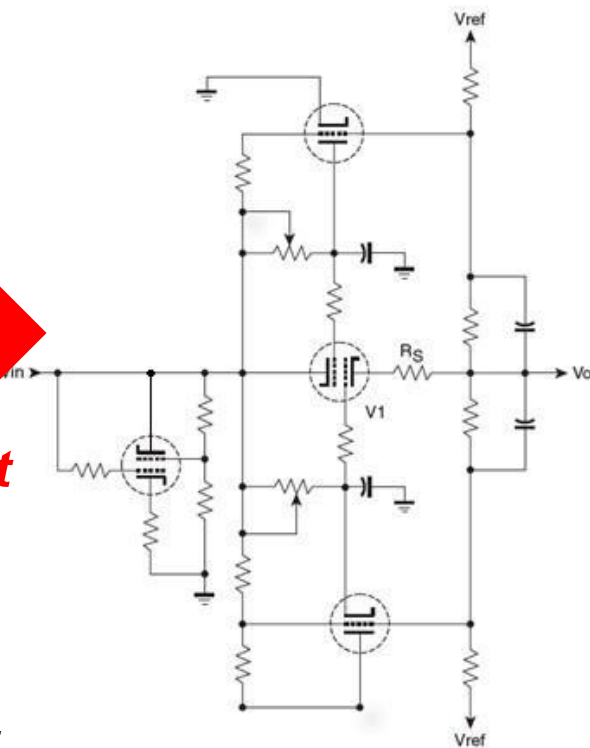
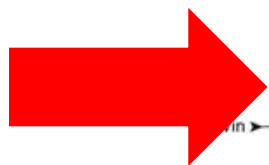
Combined Over-voltage & Over-current Limiter



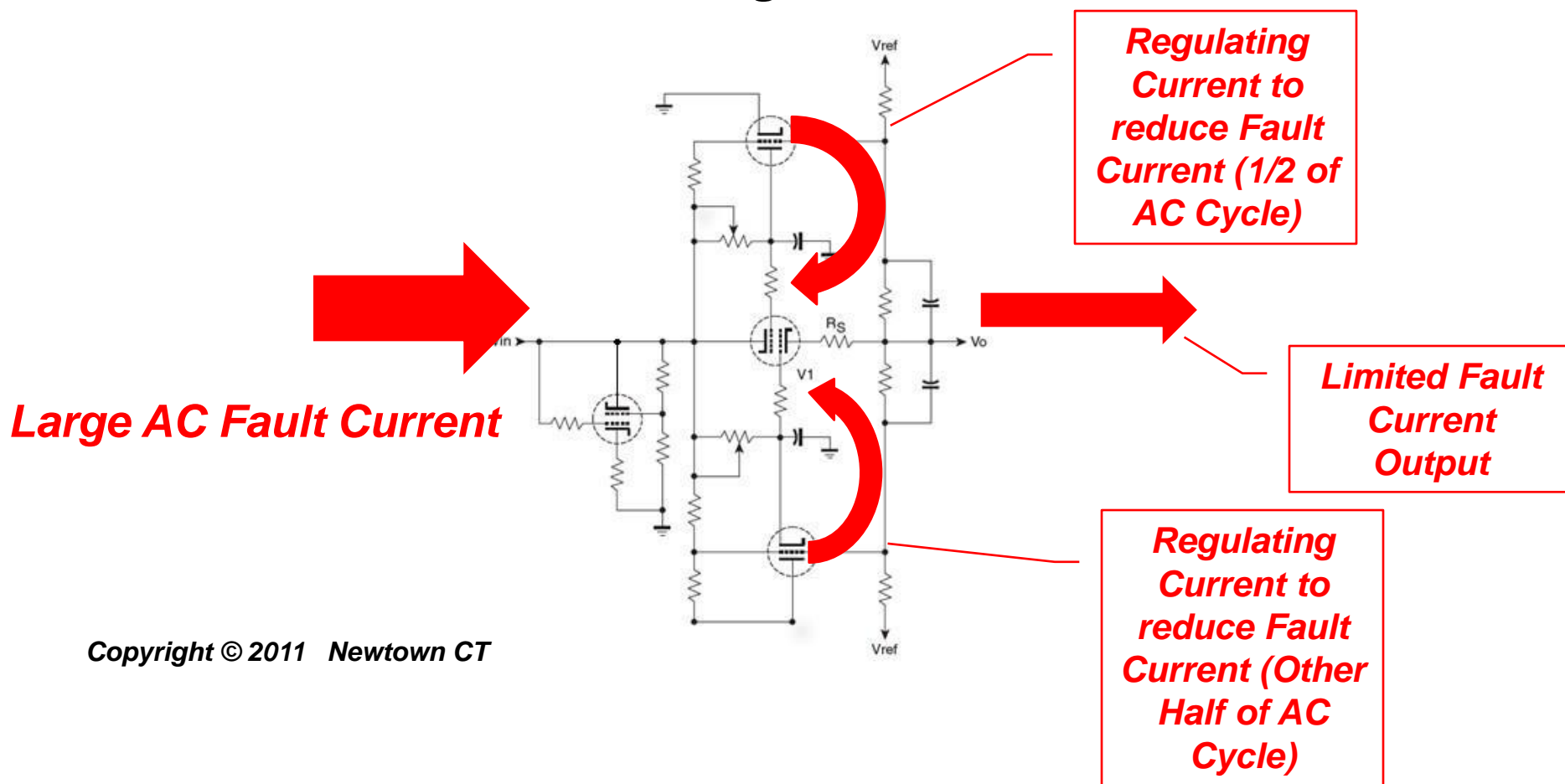
***Normal AC Current Flow
Through BiTron***

Combined Over-voltage & Over-current Limiter

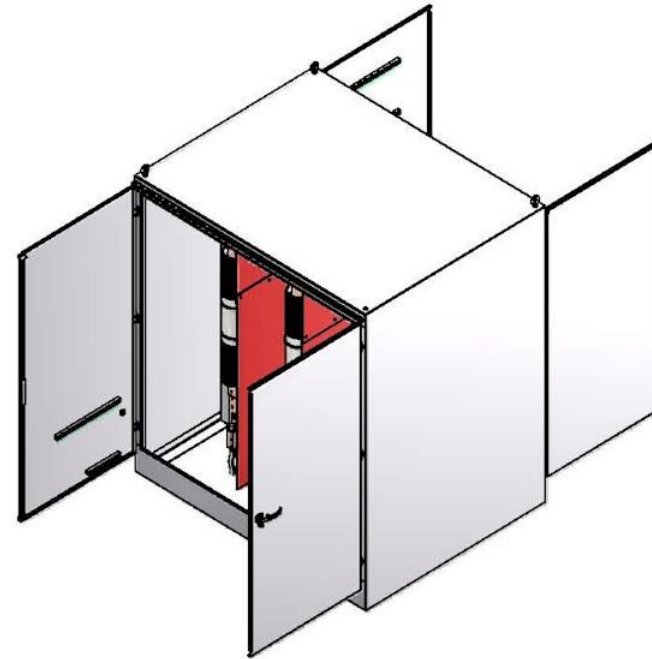
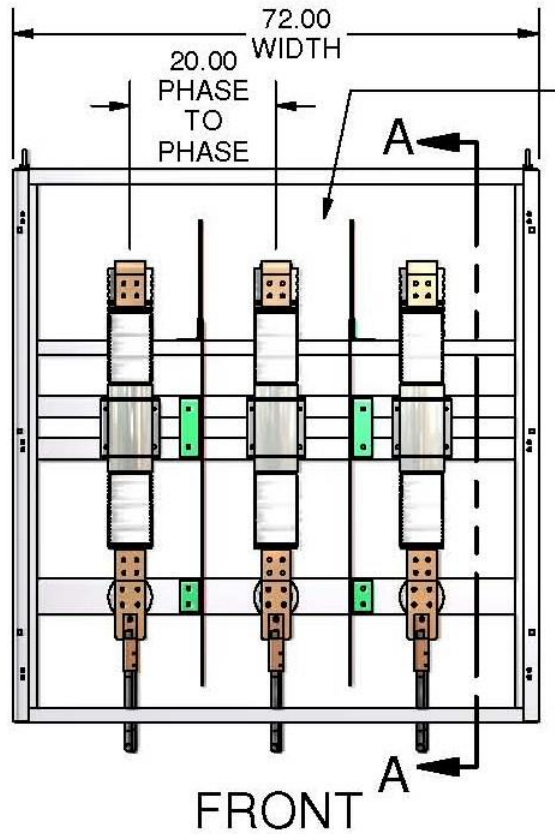
Large AC Fault Current



Combined Over-voltage & Over-current Limiter



FCL Integration 13.8 KV, 1000 A





CaptureTM

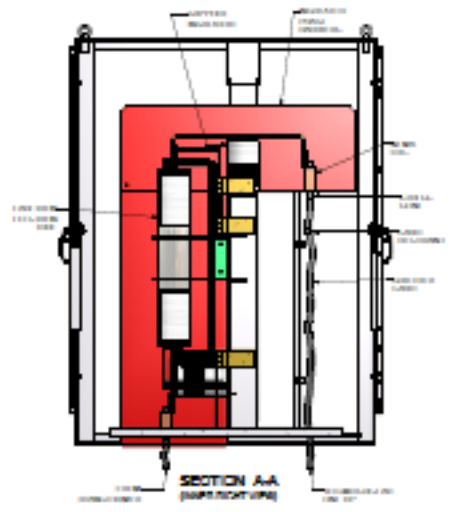
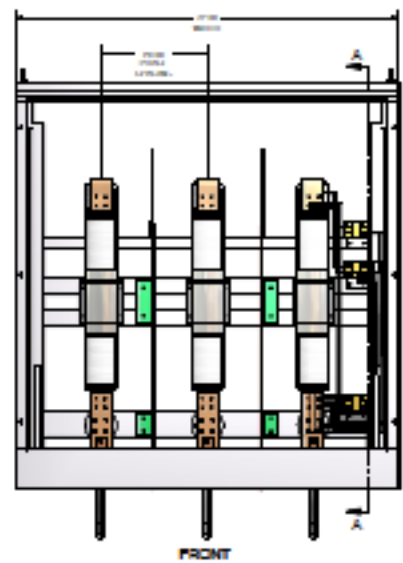
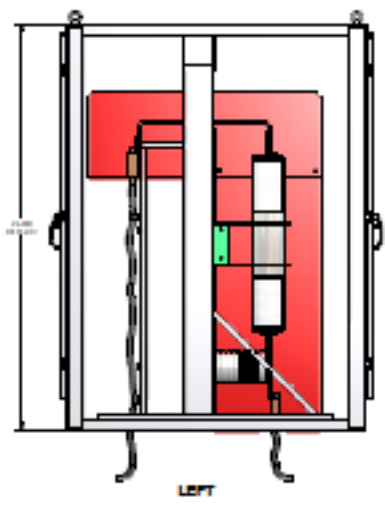
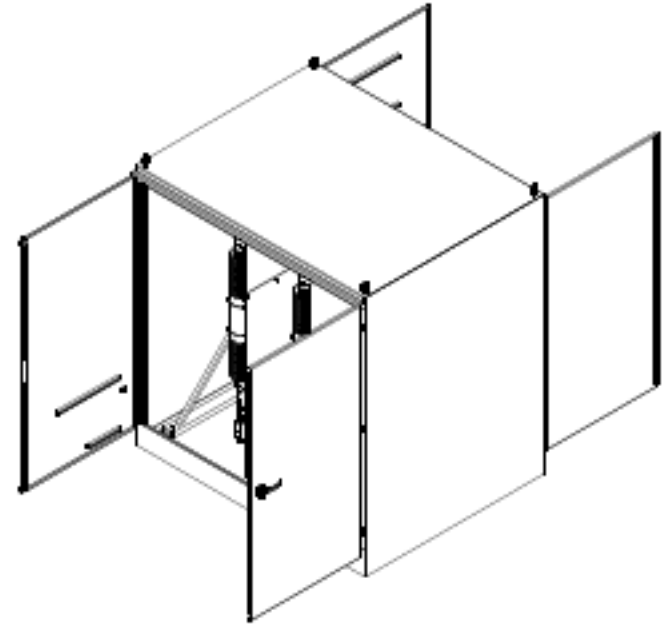
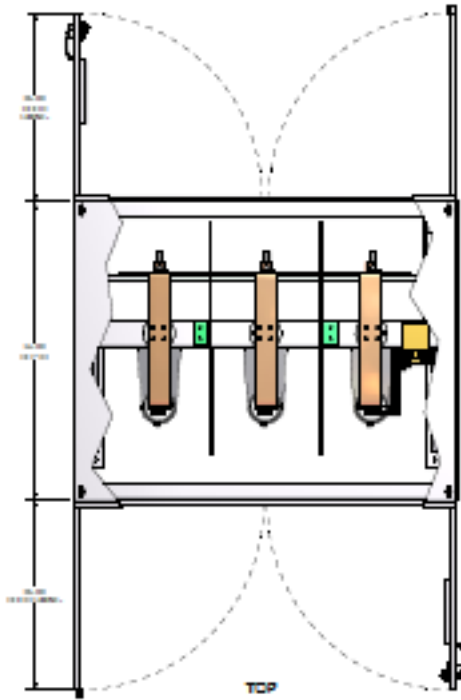
Fault Current Limiter

- Introducing a different concept – FaultronTM electron tube technology
- Passively Dynamic operation
- No fuses or parts to replace
- No breakers to reset
- Integrated monitoring control system
- 24/7 sentinel protection
- Keeps your power system functional and reliable

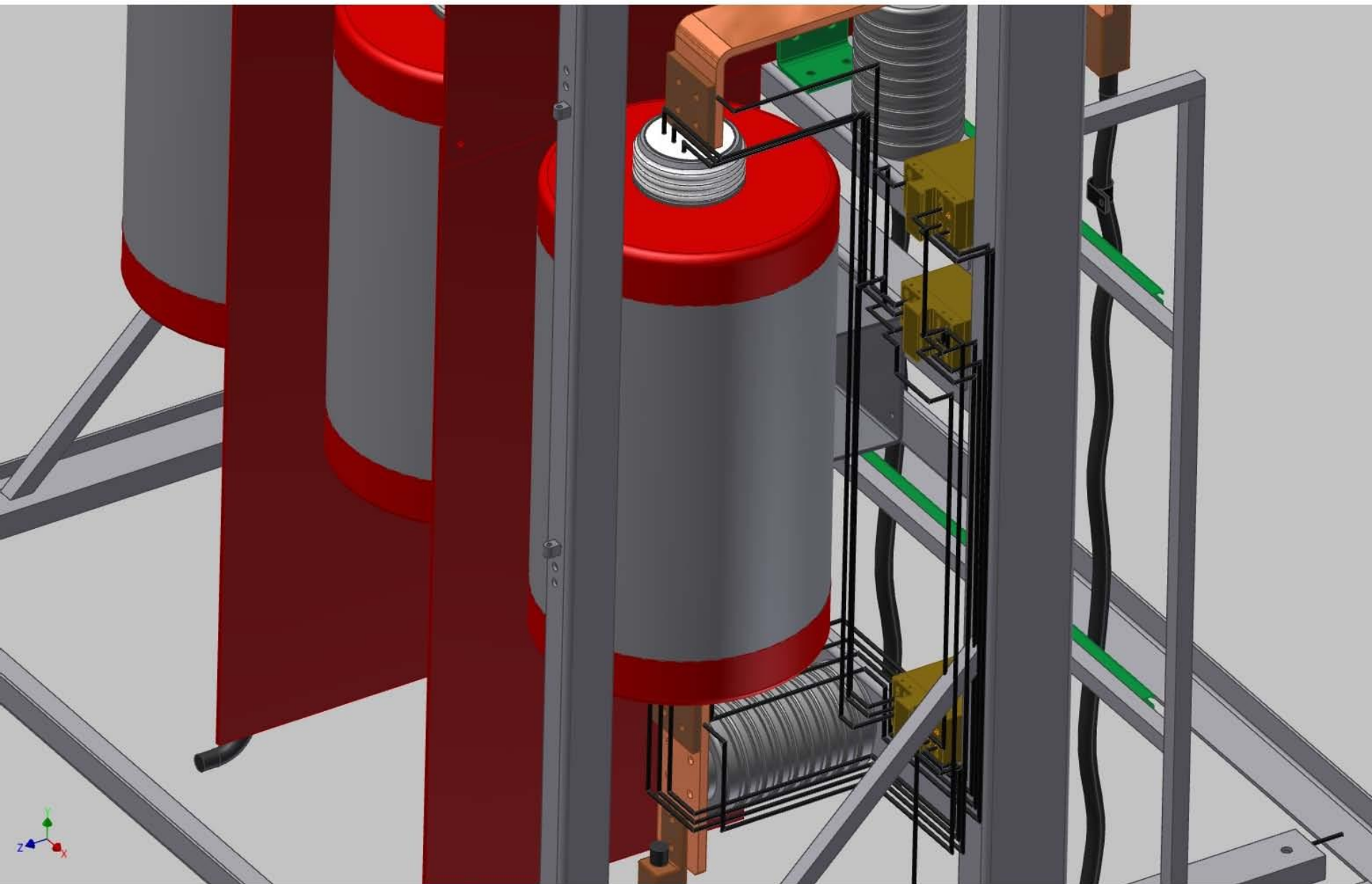


- GENERAL**
- 1. UNITS SHALL BE 100% ASSEMBLED AND TESTED AT THE MANUFACTURER'S FACILITY.
 - 2. UNITS SHALL BE 100% ASSEMBLED AND TESTED AT THE MANUFACTURER'S FACILITY.
 - 3. UNITS SHALL BE 100% ASSEMBLED AND TESTED AT THE MANUFACTURER'S FACILITY.
 - 4. UNITS SHALL BE 100% ASSEMBLED AND TESTED AT THE MANUFACTURER'S FACILITY.

- NOTES**
- 1. UNITS SHALL BE 100% ASSEMBLED AND TESTED AT THE MANUFACTURER'S FACILITY.
 - 2. UNITS SHALL BE 100% ASSEMBLED AND TESTED AT THE MANUFACTURER'S FACILITY.
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 - 5. UNITS SHALL BE 100% ASSEMBLED AND TESTED AT THE MANUFACTURER'S FACILITY.
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PRELIMINARY

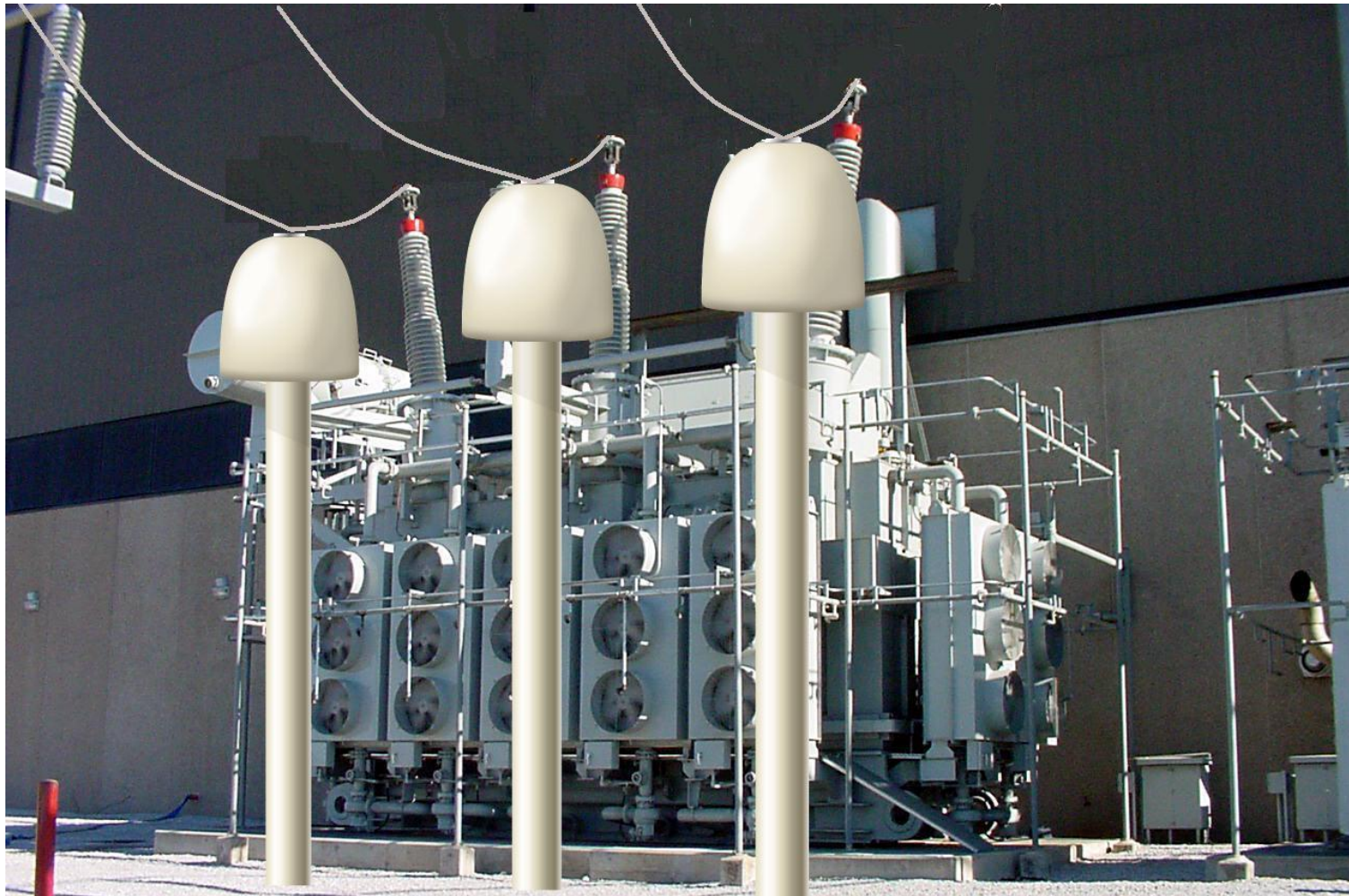




SUPER MOV REPLACEMENT

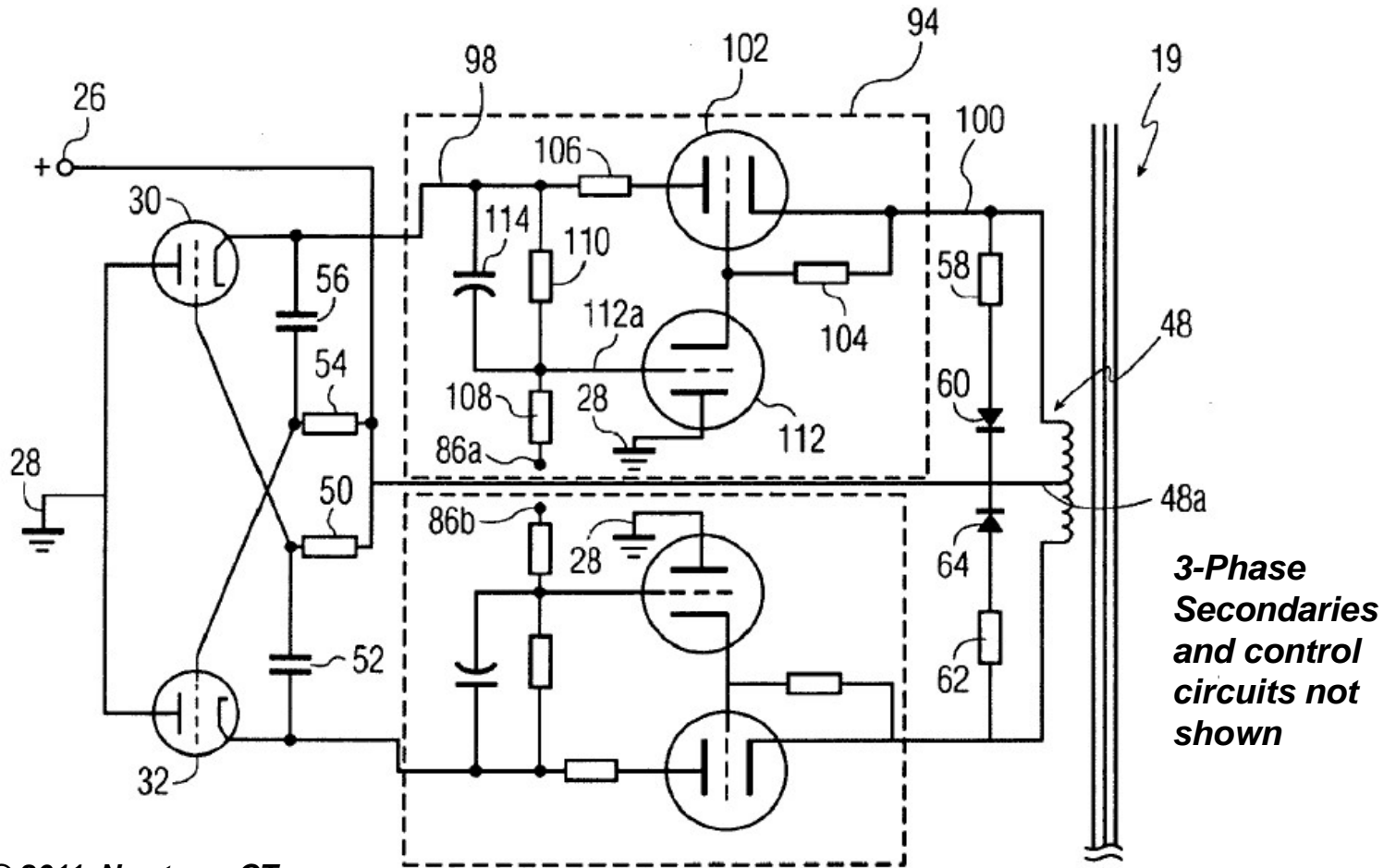


Super MOV Replacement (3-Phase; Artist Concept)

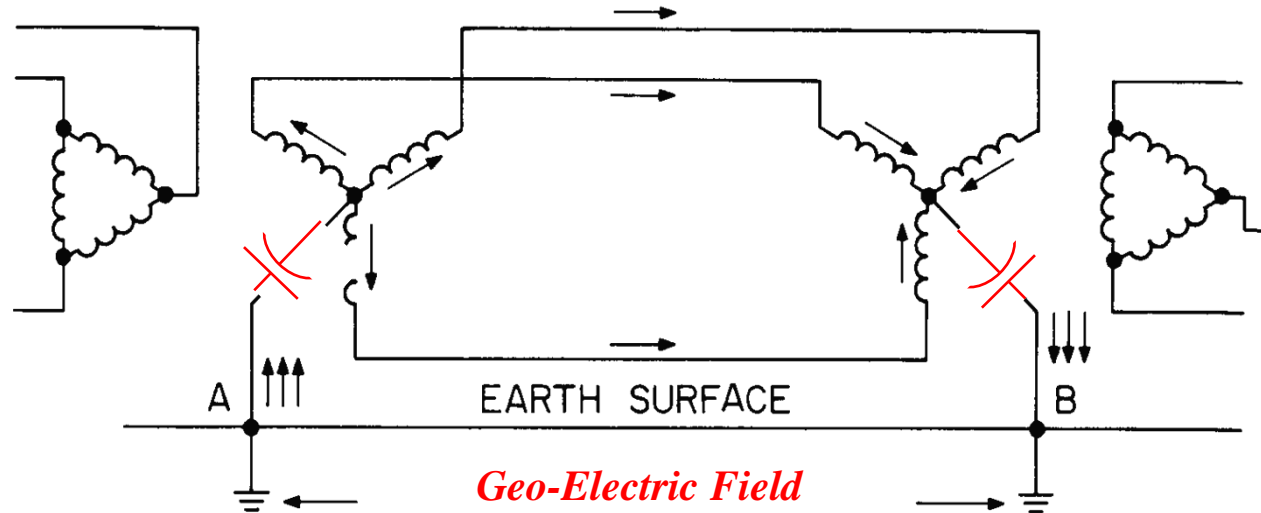




HVDC Inverter



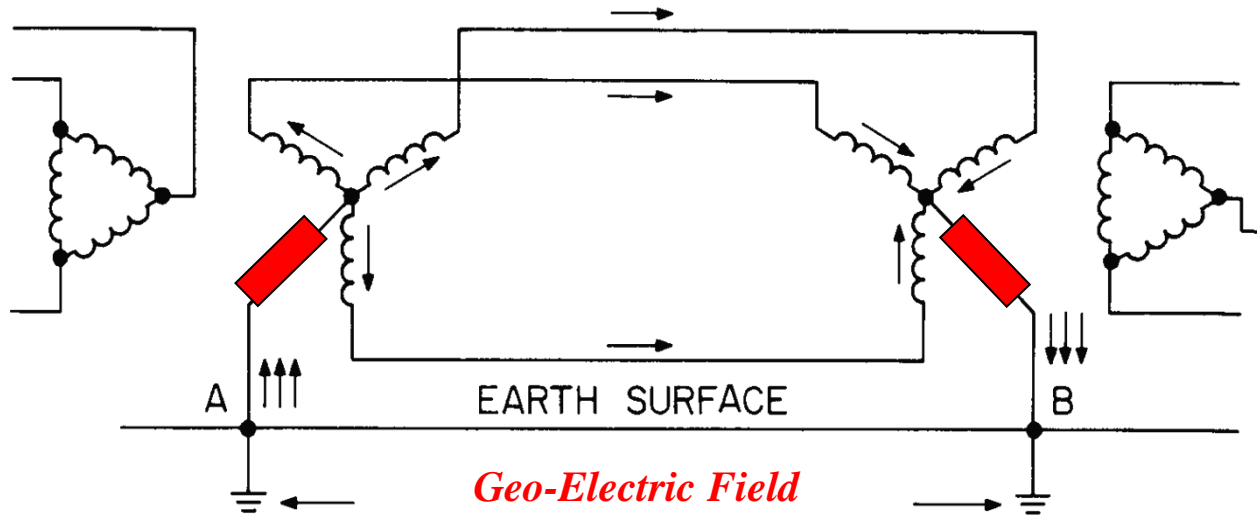
Hardening – GIC Reduction in Power Grids Transformer Neutral Capacitor Devices



A single low-voltage capacitor in the transformer neutral ground connection at each transformer will also block the GIC flow in the transmission line and each transformer.

- Capacitor needs added circuitry and sophistication for rapid AC Bypass*
- This Strategy will produce the greatest overall GIC reductions in the network*

Hardening – GIC Reduction in Power Grids Transformer Neutral Resistor



A low-ohmic resistor (2.5 to 7.5 ohms) in the transformer neutral ground connection at each transformer will act to significantly reduce but not totally block the GIC flow in the transmission line and each transformer.

NBBD Device Functional Requirements

- ***Block the flow of DC current to design DC Voltage Threat Level, while conducting low-level AC current***
- ***Must offer high reliability and not call for more maintenance than the transformers to which they are connected.***
- ***Must be able to operate autonomously and not require intervention to put them into operation under the threat circumstances they are designed to mitigate***

- ***Should not interfere with any existing protections or controls, produce new operating constraints, generate harmful interactions on the transmission system such as ferroresonance, overvoltages***

- ***Have AC fault current ratings . . .***
Adequately sized to the available fault current of the system

- ***Provide solid neutral grounding for the AC system to maintain the effectively grounded transmission system and limit the transformer neutral to less than ~20 kV peak voltage rise***

The Last Three Requirements are Technically the Most Difficult, but are readily available as Commercial Off-the-Shelf Hardware/Component Solution

Determining the DC Threat Level Requires Sophisticated Network Analysis, so that Device can be Engineered for Appropriate Withstand Levels

NCBD Device Design Specifics

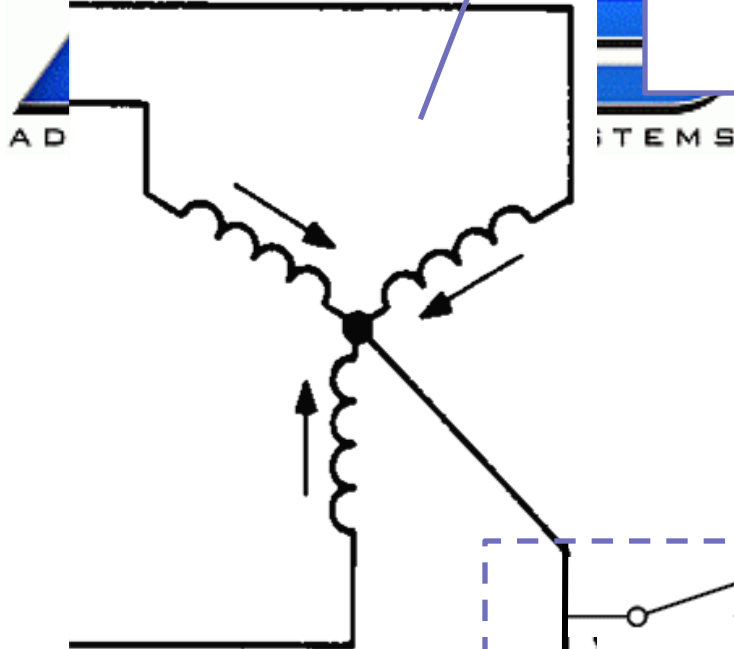
Large Power Transformer in which Neutral Capacitor and Bypass Device (NCBD) is installed

The AC ByPass Portion of the Device – Provides Momentary Path to Ground for Large AC Fault Currents – Then quickly reseals to resume DC Blocking

Mechanic al Bypass Switch Module

Capacitor Module

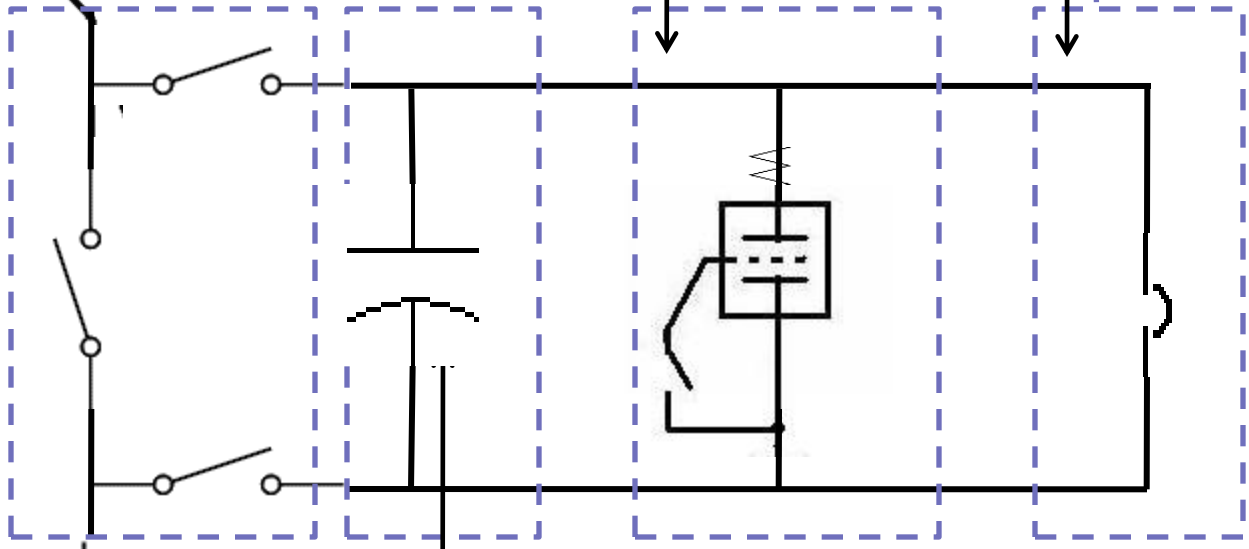
High Speed Bypass Module



Optional Device Isolation Module

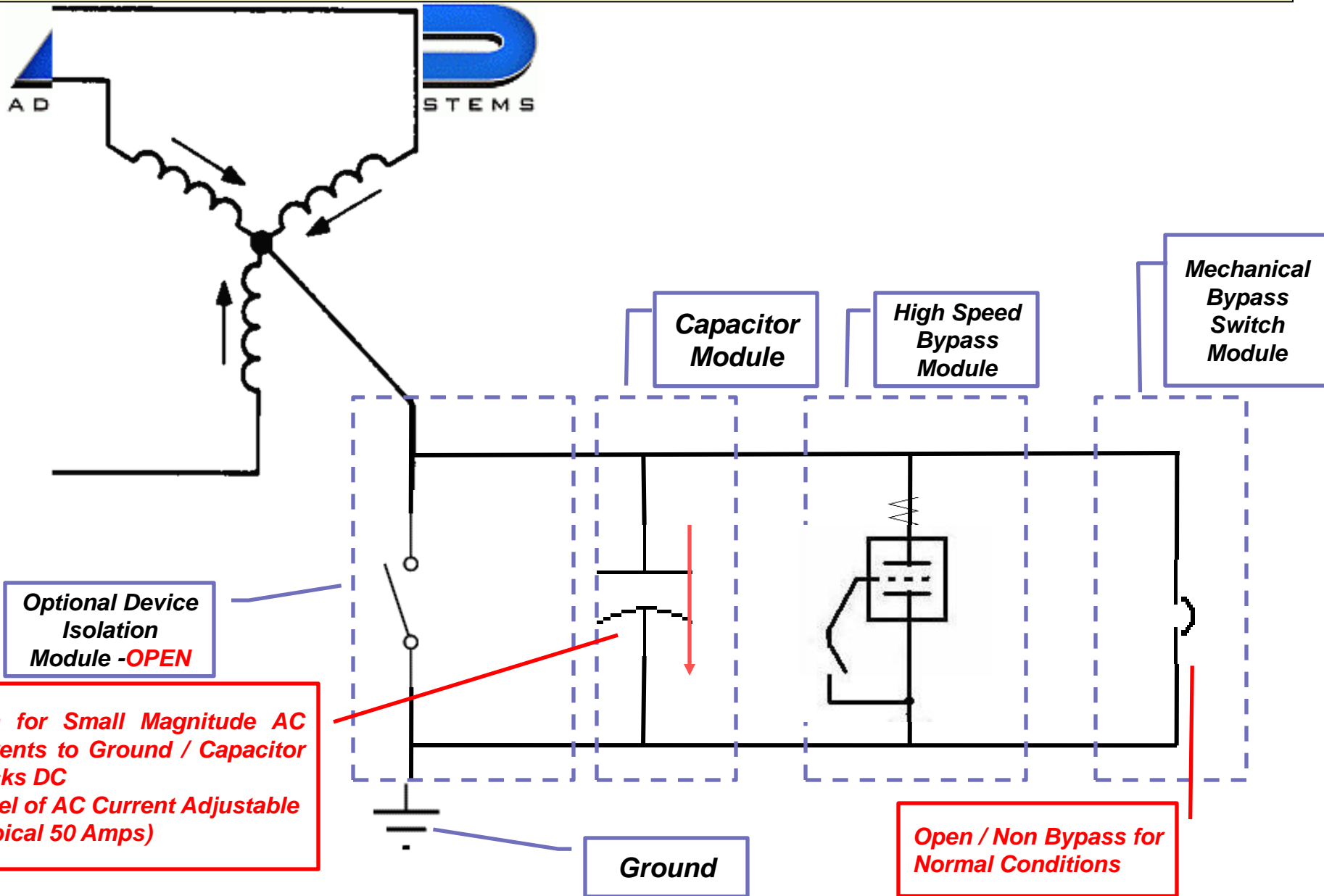
Ground

The Neutral Capacitor Portion of the Device – Blocks DC – Allows Low-Levels of AC Current to Ground (Could also be Resistor)



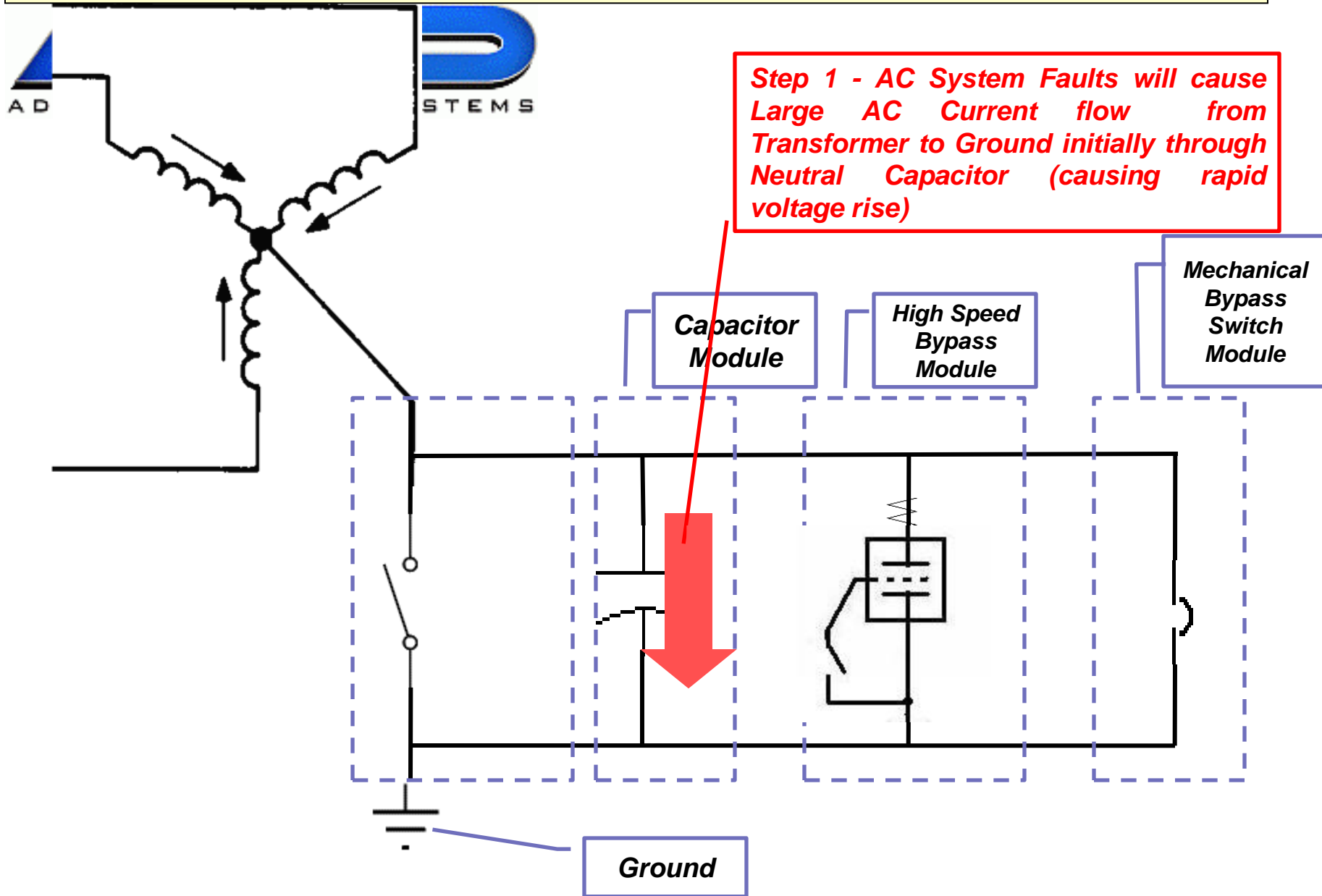
NCBD Device Operation Specifics

Normal Operation in GIC Blocking Mode



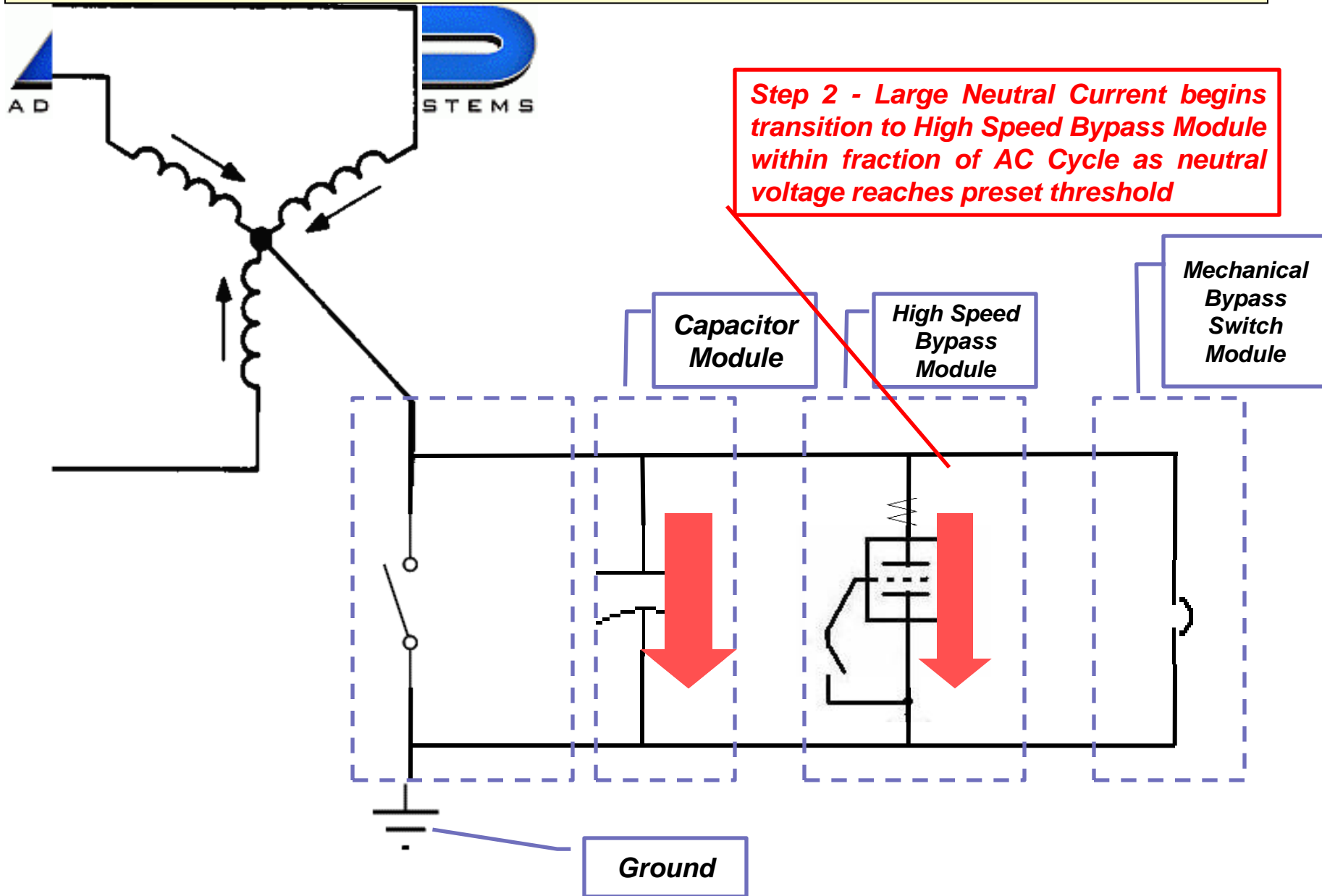
NCBD Device Operation Specifics

AC Fault Conditions – Operation in AC Bypass Mode



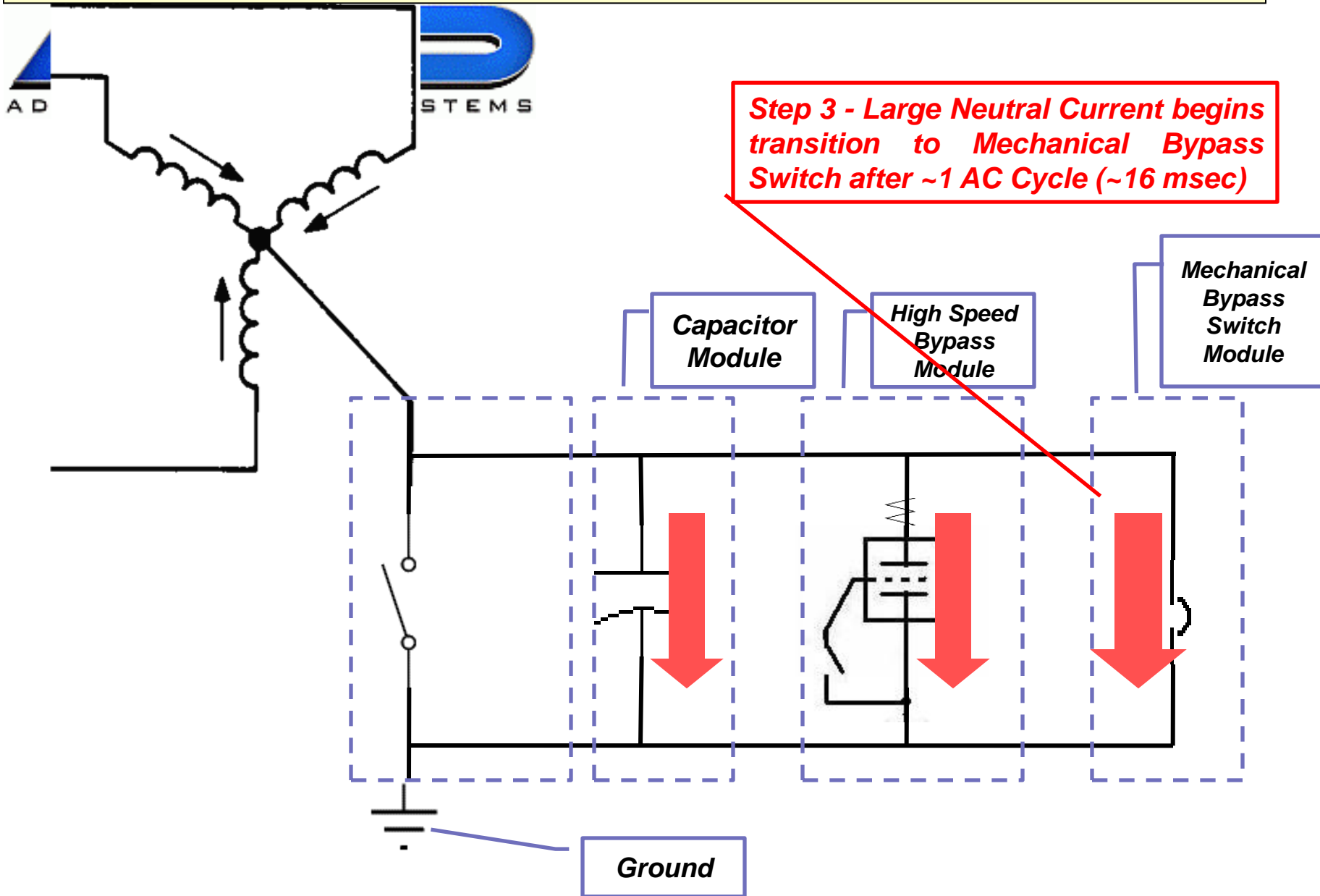
NCBD Device Operation Specifics

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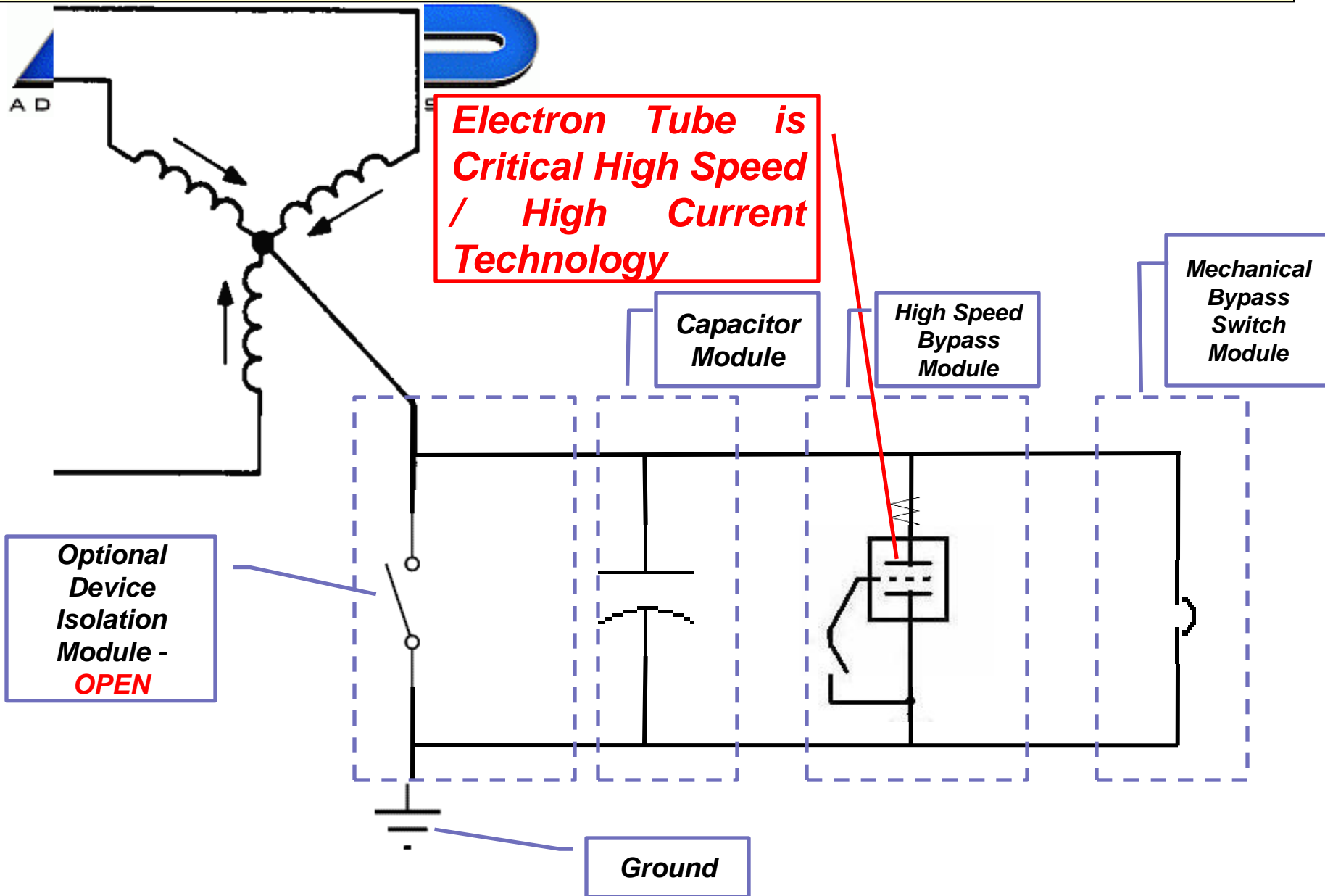
NCBD Device Operation Specifics

AC Fault Conditions – Operation in AC Bypass Mode



NCBD Device Operation Specifics

Normal Operation in GIC Blocking Mode



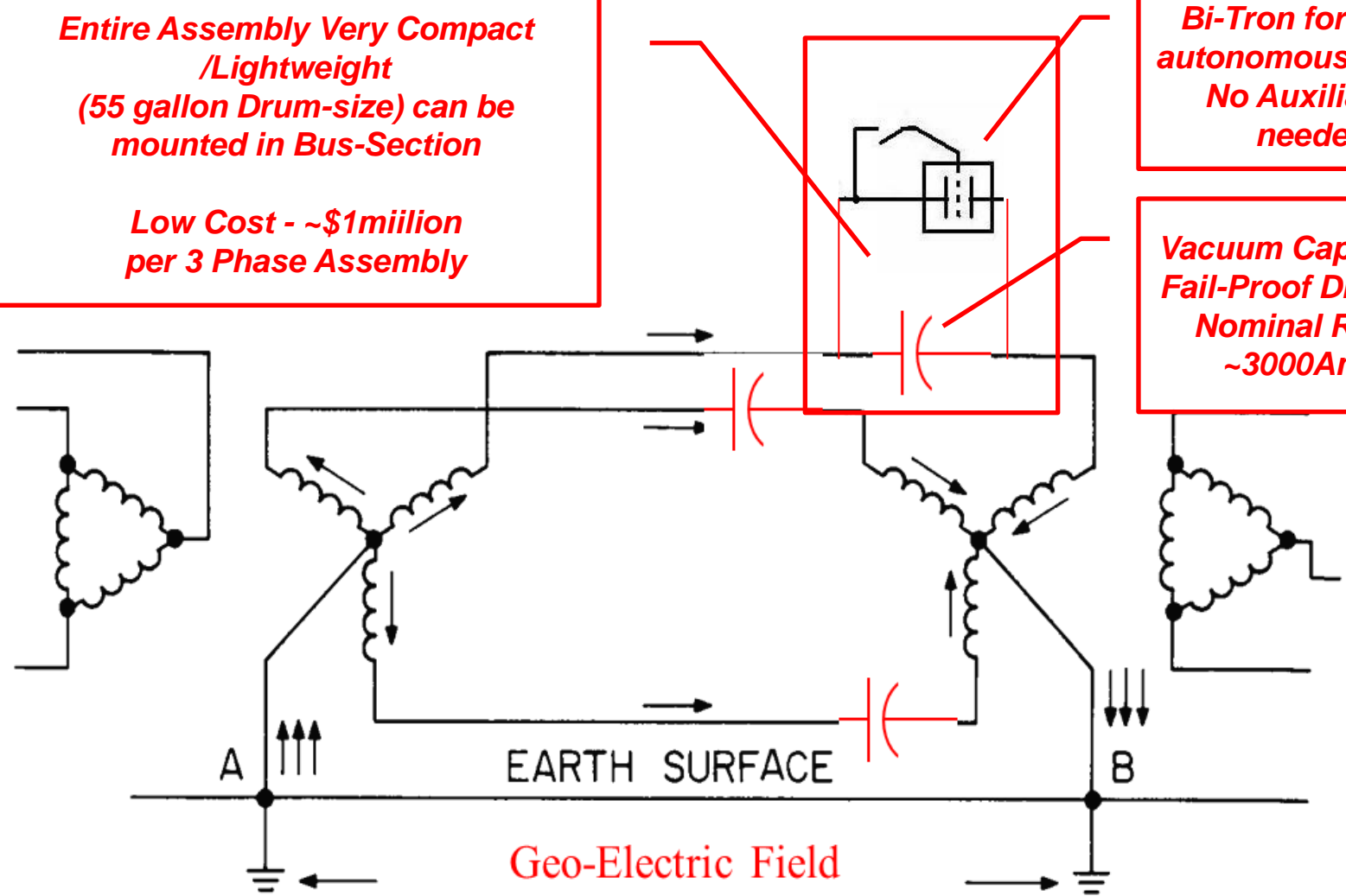
Inexpensive, Compact and Fully Autonomous Transmission Line Series Capacitor Bi-Tron Bypass and Vacuum Capacitor

***Entire Assembly Very Compact
/Lightweight
(55 gallon Drum-size) can be
mounted in Bus-Section***

***Low Cost - ~\$1million
per 3 Phase Assembly***

***Bi-Tron for Rapid
autonomous bypass
No Auxiliaries
needed***

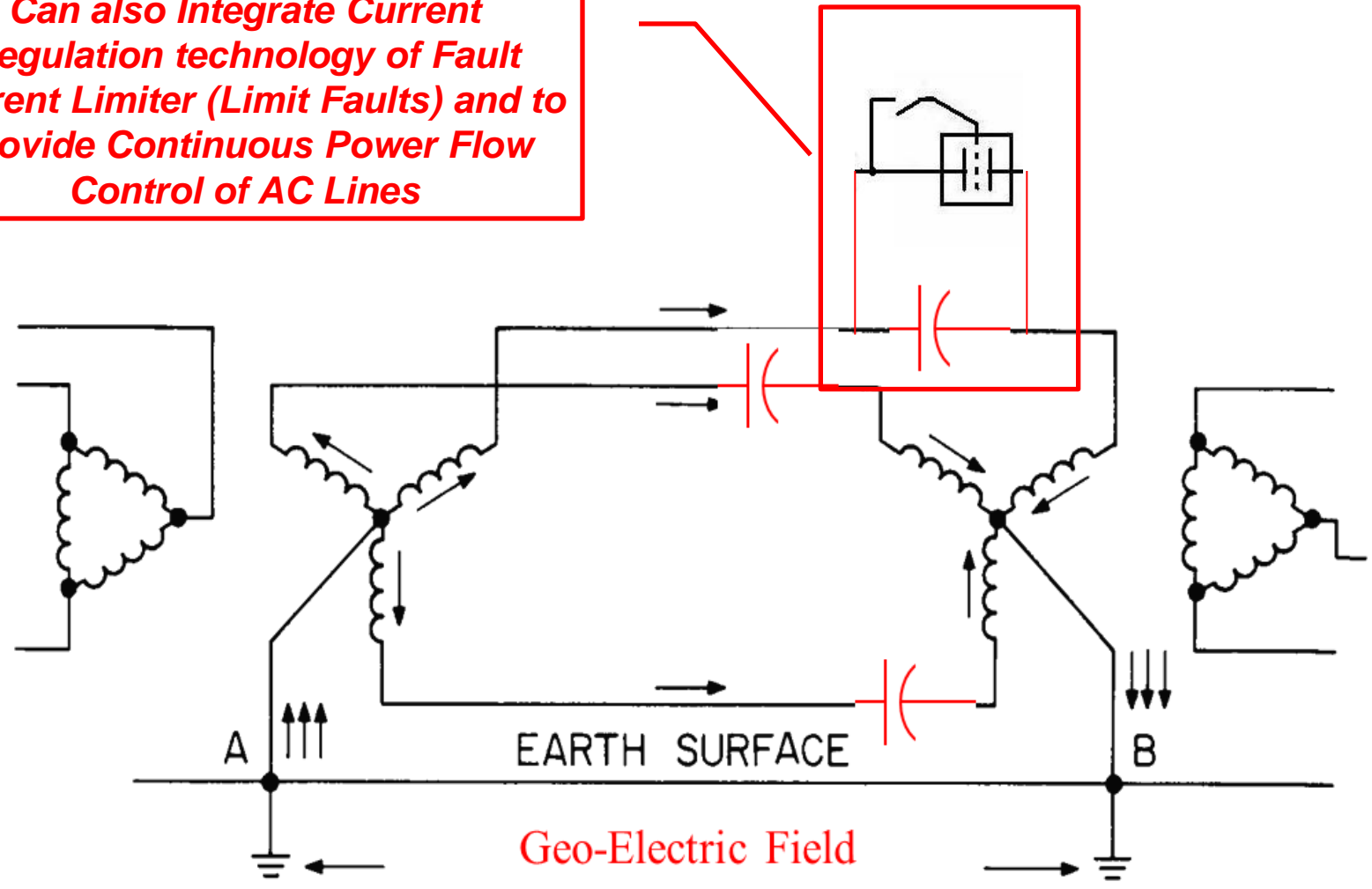
***Vacuum Capacitor –
Fail-Proof Dielectric
Nominal Rating
~3000Amps***



Inexpensive, Compact and Fully Autonomous Transmission Line Series Capacitor Bi-Tron Bypass and Vacuum Capacitor



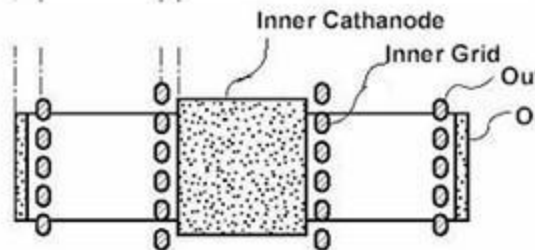
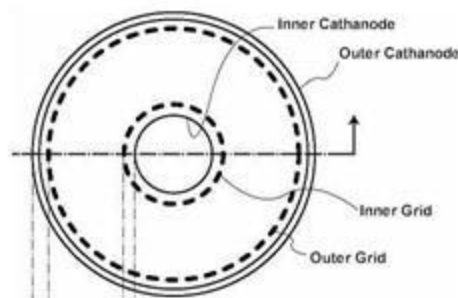
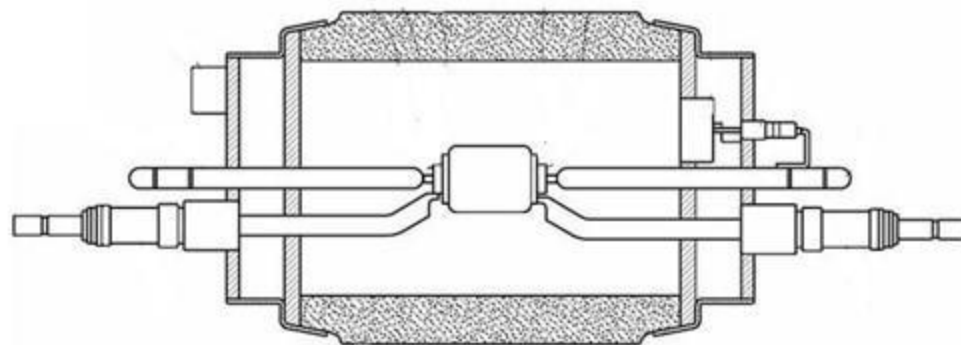
Can also Integrate Current Regulation technology of Fault Current Limiter (Limit Faults) and to Provide Continuous Power Flow Control of AC Lines



Example 4275 Bi-tron Tube



4275 Bi-tron™



Some structures omit

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Ratings

30kV

75kA

- **Significantly faster than semiconductor**
- **Bi-directional operation**

• **Nominal size of 12" L, 5" dia**

• **Scalable to larger KA and KV Ratings and sizes**



***ABOUT
ADVANCED FUSION SYSTEMS LLC***

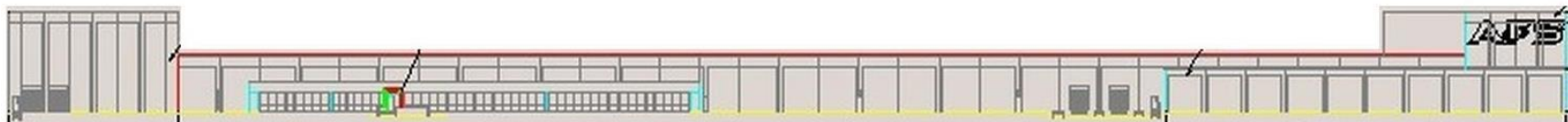


AFS Overview

- Advanced Fusion Systems LLC (AFS) was formed in 2008 to develop and exploit patent-pending and proprietary technologies to produce a series of related products:
 - *Faultron™ Fault Current & Over-Voltage Limiters*
 - *FXI Environmental Remediation Systems*
 - *Electromagnetic Pulse (EMP) Protection systems*
 - *GIC Protection Systems*
 - *Pulse Power-Based Systems*
 - *Advanced Electron Tubes*
- *All technologies are US and International Patents-Pending.*
- *AFS has acquired the assets of Hudson Research Inc which is now a subsidiary.*
- *AFS has acquired the assets of Thryonics Inc which is now a subsidiary.*
- *AFS has acquired and is modifying a 250,000 sq. foot facility in Connecticut .*
- *AFS is a privately-held Delaware limited liability corporation.*



AFS New Facility



Expanded facility ↑↑

Satellite view of
<< existing facility

- (4) FCL Test to 345 KV
- (2) EMP Test to 1.2 MV AC/DC @ 250 KV/M
- Radiation Lab 1 MeV & EMP
- EMP & RF Anechoic

11 Edmond Rd, Newtown, CT. 250,000 ft² (including expansions)



Under Construction



>35,000' of 5" conduit; >10,000 cubic yards of concrete



Specialized Test Facilities

- 20 MW power feed to fully shielded test facility
 - (scheduled expansion to 40 MW)
- Fault Current Test Cells: 4160 V – 345 KV
 - On-site 10 MW Generator
 - Armored & Shielded FCL Test Cells
- Radiation Lab: 1 MeV; 100'L x 34'W x 20'H;
 - 3 foot thick concrete walls
 - Full EMP Shielding (Electric & Magnetic)
- EMP Test Cells: Electric & Magnetic Shielding; 250 KV/M sources)
 - (2) @ 135' x 50' x 50';
 - (1) @ 80' x 40' x 22' (also RF anechoic)
- Site Safety includes:
 - Interior and exterior E & H Field monitoring
 - Interior and exterior X-ray monitoring



FCL Test Facilities

- This facility will support Fault Current testing from 4160V to >345KV.
- FCL Test Cell 1: 4160 & 13.8 KV @ 1 MW
- FCL Test Cell 2: 13.8 KV & 25 KV @ 10 MW
- FCL Test Cell 3: 33 KV – 69 KV @ 10 MW
- HV Lab: 115 KV – 345 KV @ 10 MW
- Future Expansion: 500 KV – 1.2 MV @ >10MW
- All FCL test cells use custom-designed transformers.
- Testing to IEC specs where available.



EMP/GIC Test Facility

- It is essential that all devices be tested under realistic conditions, but there are no EMP test facilities capable of on-load testing devices up to 1 million volts (that we are aware of).
- As part of our commitment to the EMP protection arena, AFS is constructing a world-class EMP test facility.
- This facility will be capable of testing devices at line voltages up to 1.2 million VAC or VDC, under load conditions of up to 10 MW, and in a sub-100 picosecond risetime pulsed electric field environment of >250 KV/m.
- This facility will test in excess of the Mil-188-125 standard so as to provide realistic IEMP conditions.
- This facility can successfully create SGEMP environment.
- This facility also does fault-current testing, flashover, and other tests..



Advanced Manufacturing Capabilities



Advanced Manufacturing Capabilities

- CNC Machining: 7-axis, 5-axis, & 4-axis systems (micron tolerances)
- Electron Tube Processing
- Electrochemical Processing
- Vacuum-grade Reinforced Ceramics
- Cathode Fabrication
- Glass Fabrication
- Ultra-High-Speed Electronics
- Optical Fabrication
- Thin-Film Processing; Reactive Ion Plating
- Plasma Processing
- Welding, Brazing, Silver Soldering
- Electronics fabrication
- Precision Assembly
- Vacuum System & Device Fabrication

- This is a photo of our large CNC machine.
- It is a fully computerized 7-axis machining center.
- Machining tolerance is 0.00005" over 25 feet.
- It can handle parts up to 7 feet in diameter, up to 25 feet long, weighing over 35 tons.
- This machine itself is 65 feet long and weighs 85,000 pounds.
- A sister machine has been acquired for deep boring to 25 foot depth.
- A very large milling machine, 6' x 14' x 10'.



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Electron Tube Manufacturing

- AFS and its subsidiaries have the most advanced electron tube processing capability in the US.
- The machine shown at right is a processing station capable of processing five Pulsatron-size triodes simultaneously.
- Our ability to custom build processing equipment coupled with our extraordinary machining and chemical processing technology allows us to build electron tubes of virtually any size, a capability that no other company in the US has.
- AFS is the only manufacturer of direct electrically driven X-ray lasers.
 - A 100 KeV 50 KJ (x-ray output) unit is under design and will be built and tested during 2012.



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Advanced Manufacturing (2)

- All critical components are manufactured in-house.
- This manufacturing is supported by a world-class Quality Assurance systems to ensure “Zero-Defects.”
- We use 100% inspection and test for all products.
- **All AFS protection devices are tested in our test facility and certified under realistic load conditions to guarantee operability. Customers are welcome to witness this certification procedure.**
- Each unit comes with performance documentation.



Thin Film Coating



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